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**Inada et al.**

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(54) **HIGH ENERGY ION IMPLANTER, BEAM  
CURRENT ADJUSTER, AND BEAM  
CURRENT ADJUSTMENT METHOD**

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(2013.01); **H01J 2237/24535** (2013.01); **H01J**  
**2237/304** (2013.01)

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**H01J 37/20**; **C23C 14/48**

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250/423 R, 492.1, 491.1, 492.23, 398,  
250/442.11, 492.22; 438/514; 315/505

See application file for complete search history.

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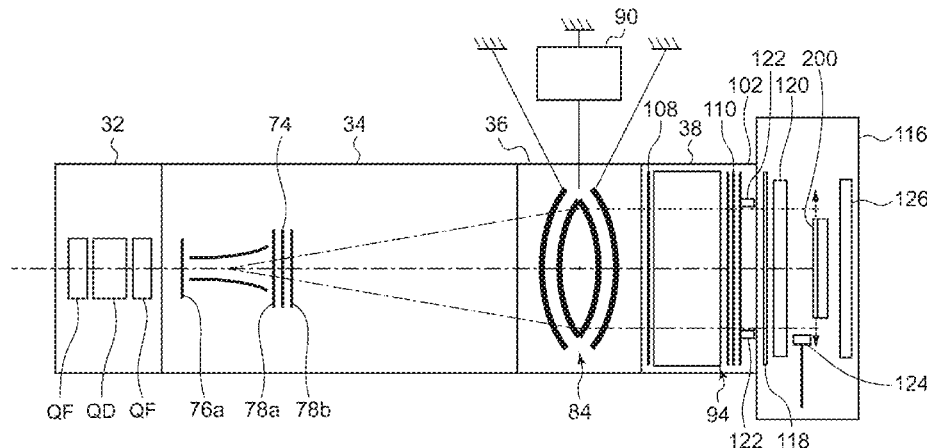
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LLP

(57) **ABSTRACT**

A beam current adjuster for an ion implanter includes a variable aperture device which is disposed at an ion beam focus point or a vicinity thereof. The variable aperture device is configured to adjust an ion beam width in a direction perpendicular to an ion beam focusing direction at the focus point in order to control an implanting beam current. The variable aperture device may be disposed immediately downstream of a mass analysis slit. The beam current adjuster may be provided with a high energy ion implanter including a high energy multistage linear acceleration unit.

**14 Claims, 23 Drawing Sheets**



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FIG. 1

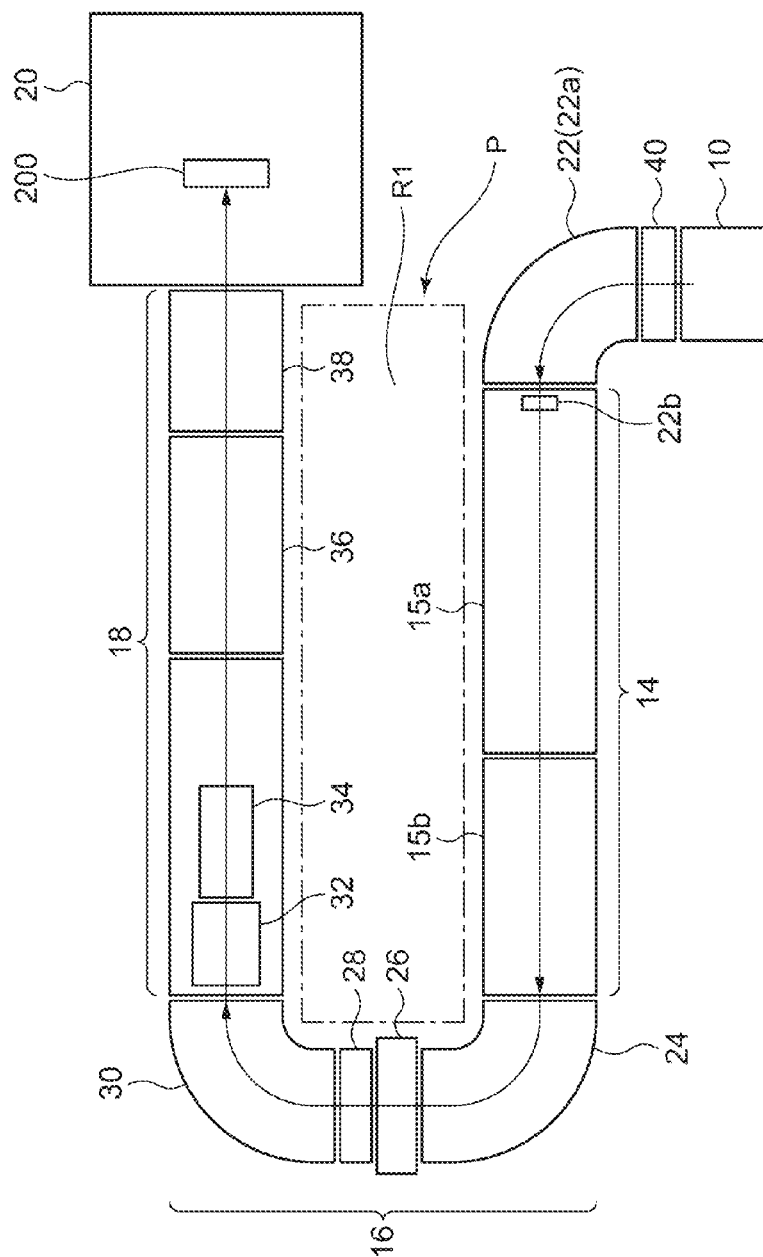


FIG.2A

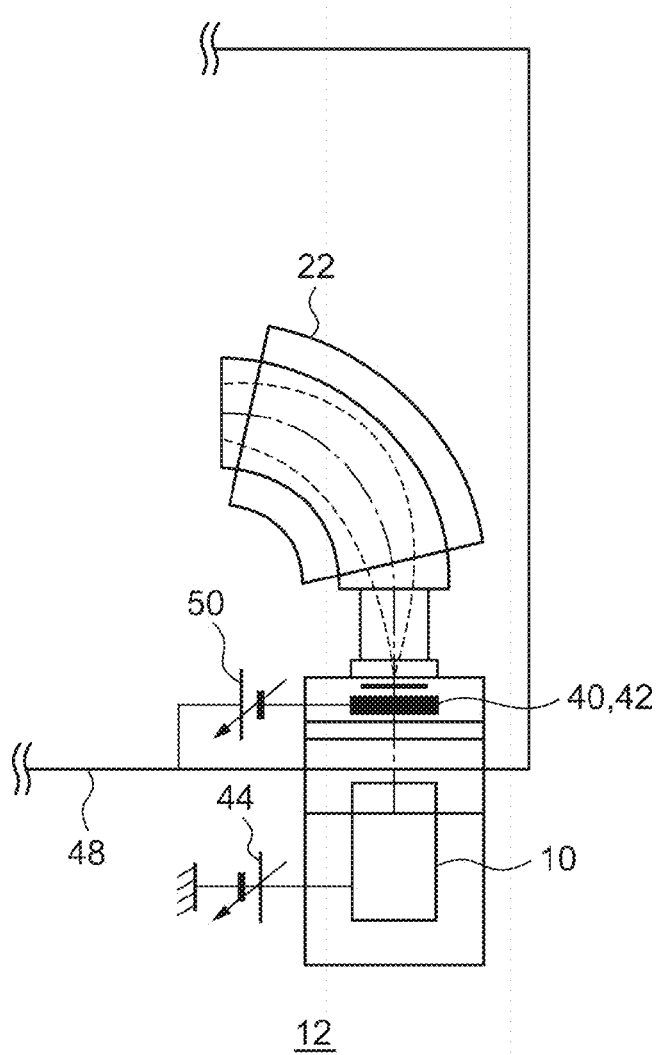


FIG.2B

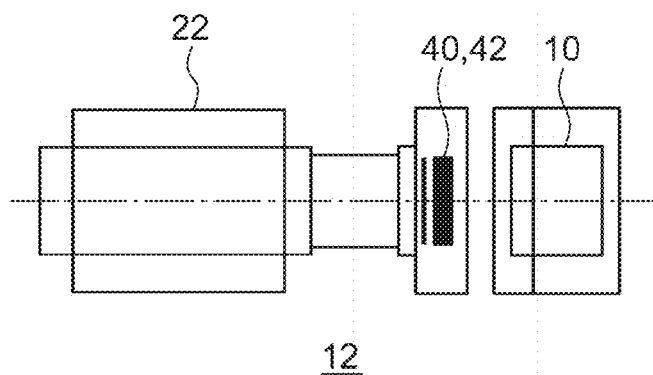


FIG. 3

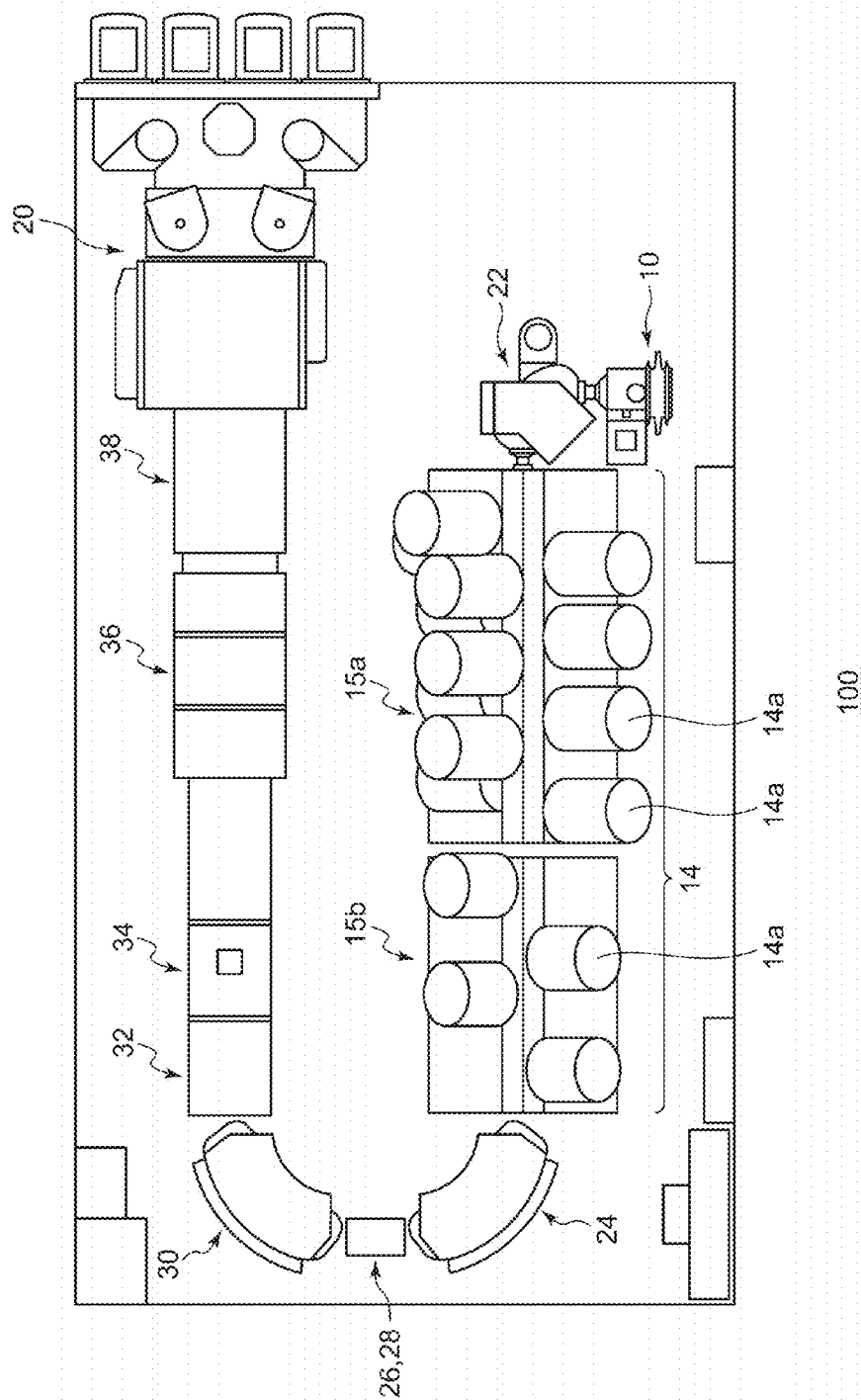


FIG. 4

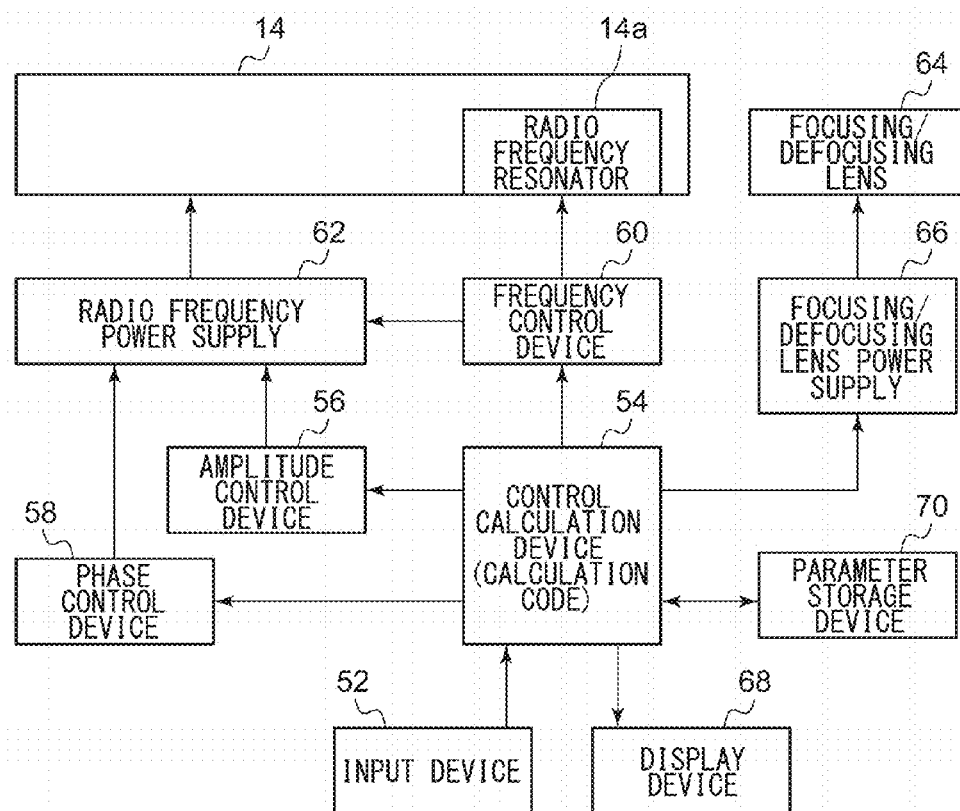


FIG. 5A

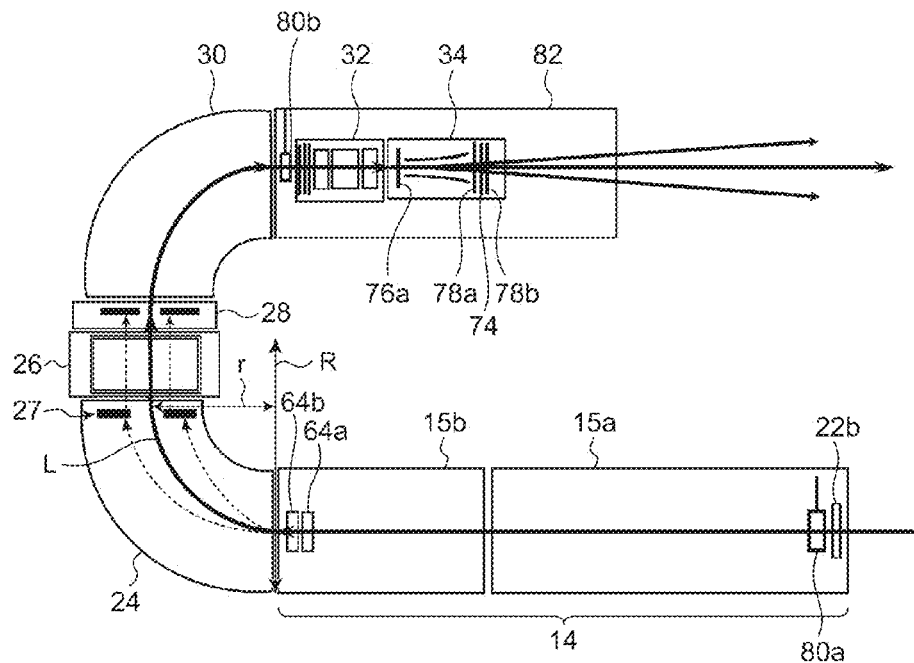
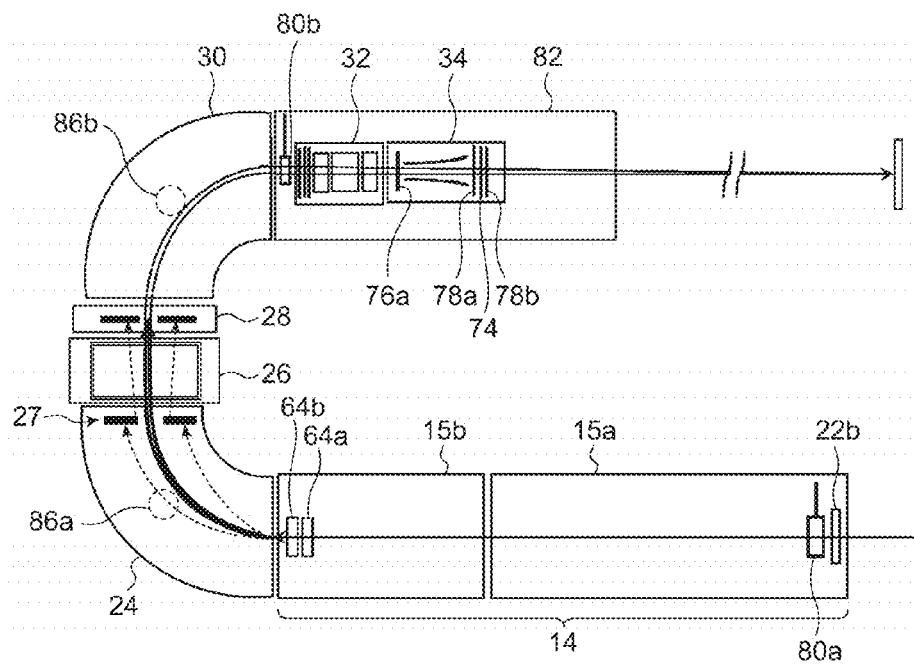


FIG. 5B



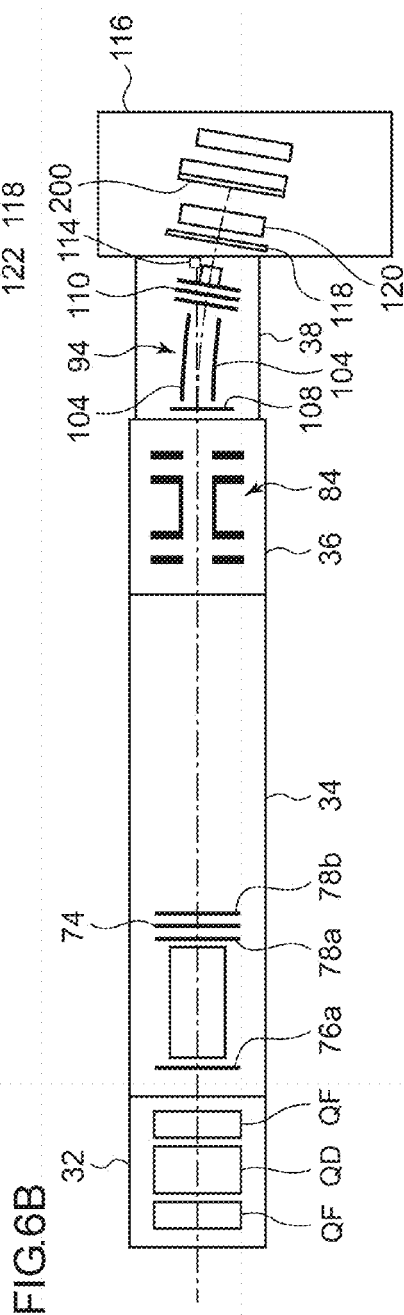
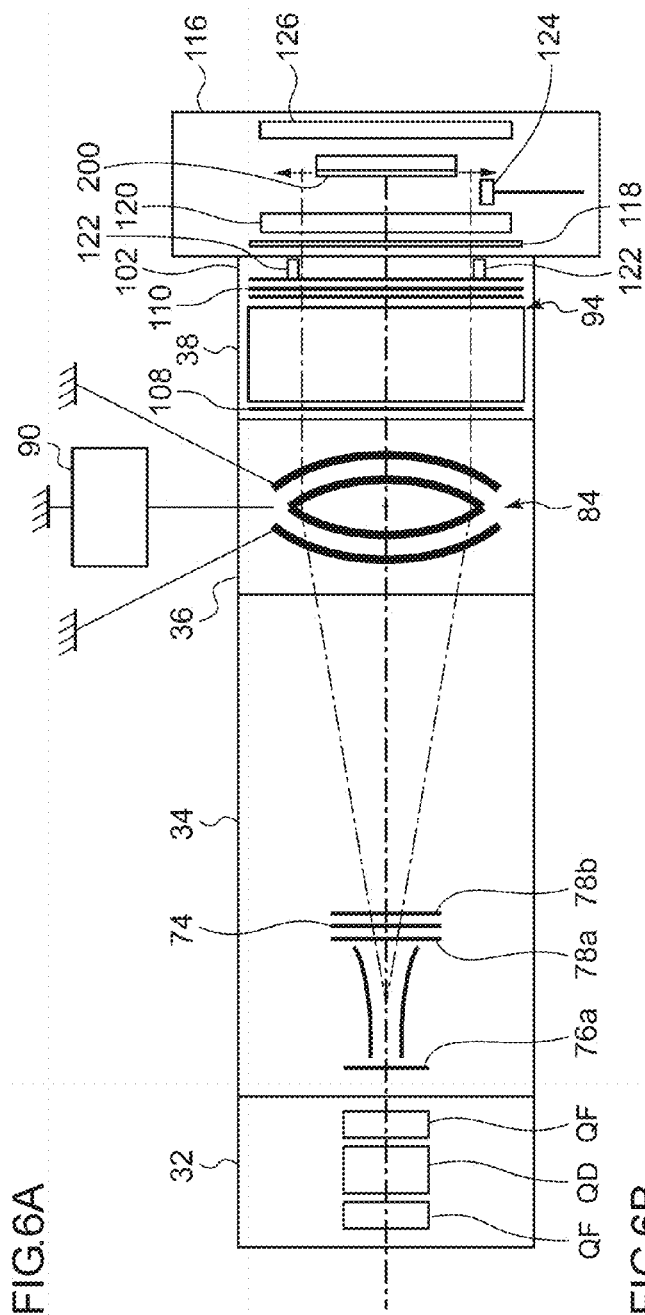




FIG.7

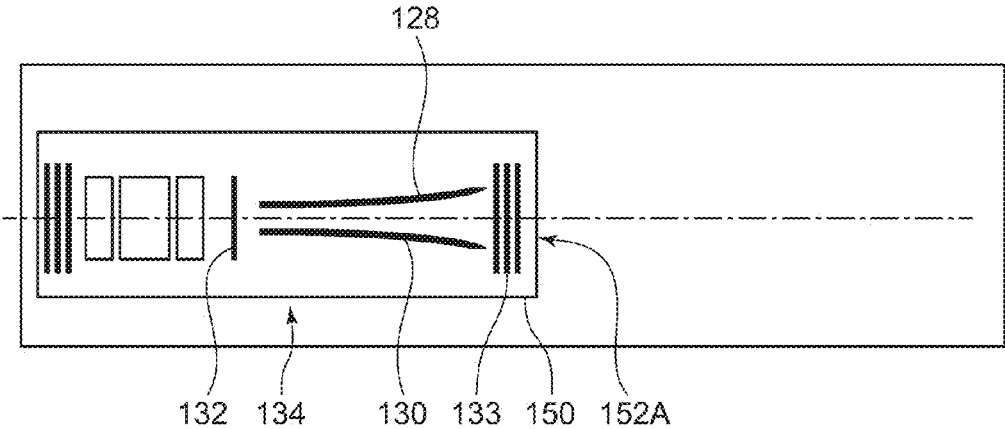


FIG.8

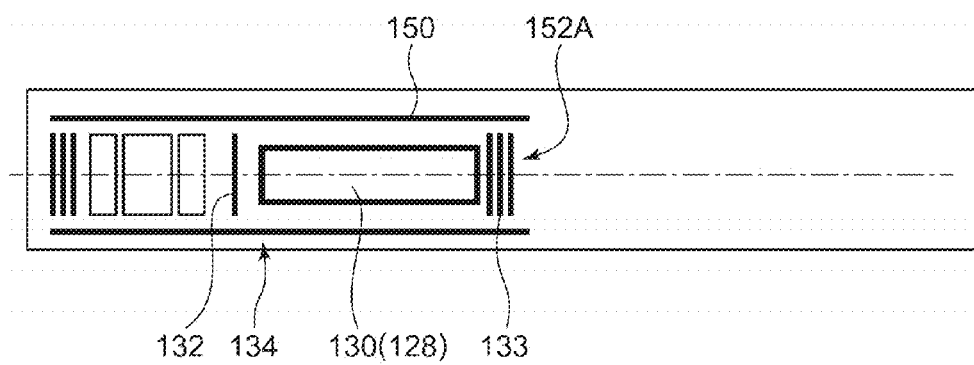


FIG. 9

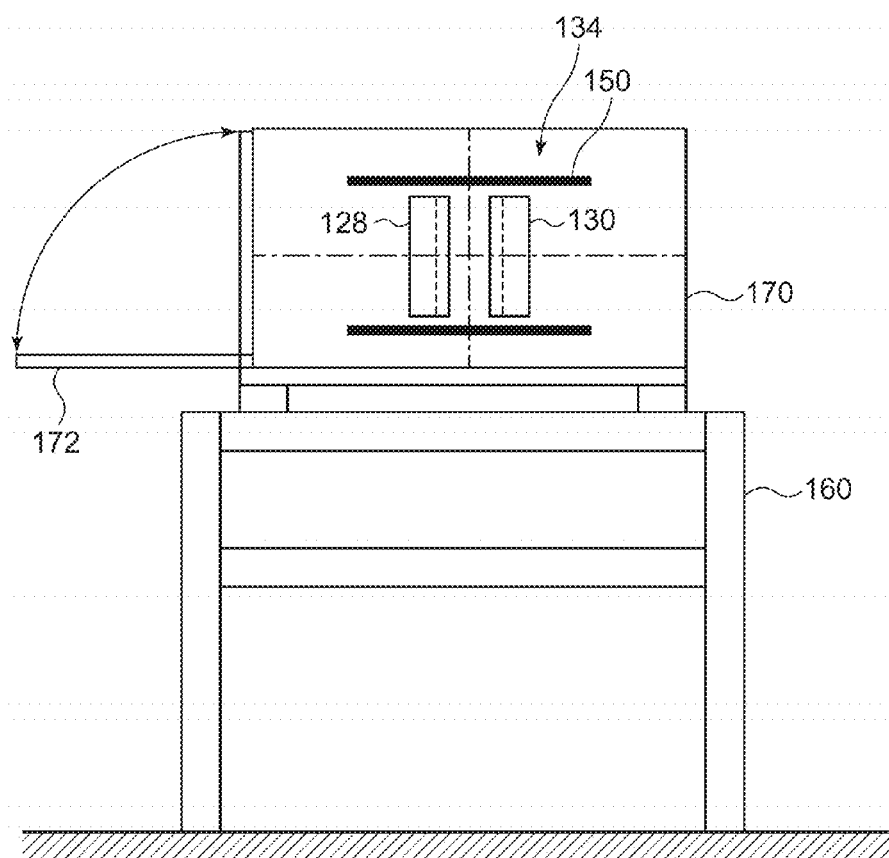


FIG.10

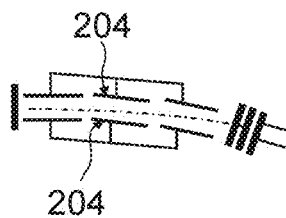


FIG.11A

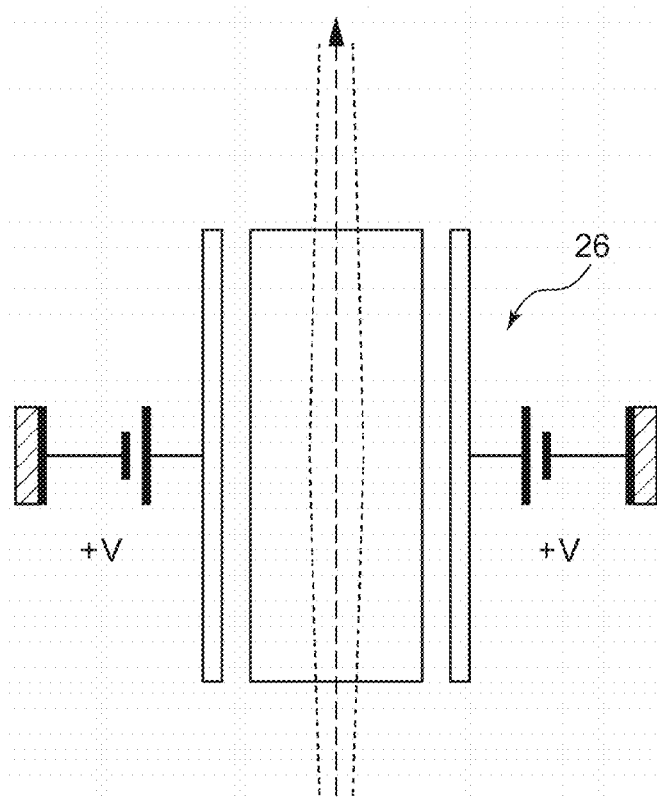


FIG.11B

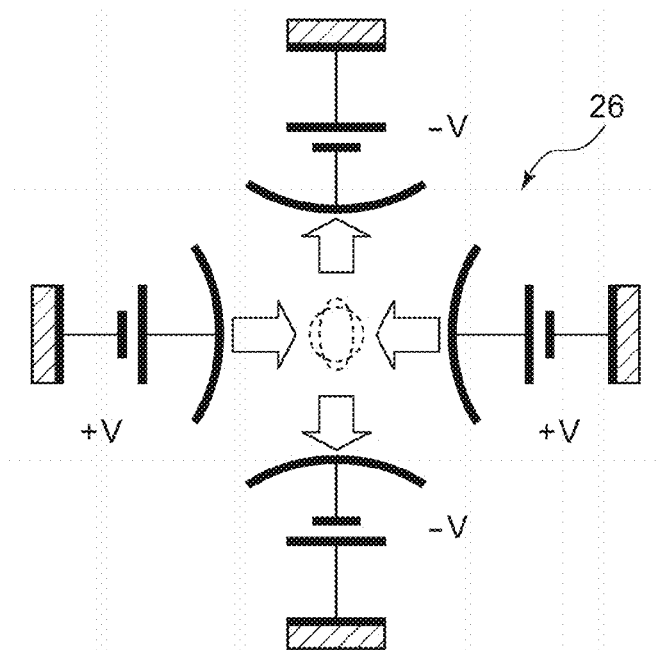
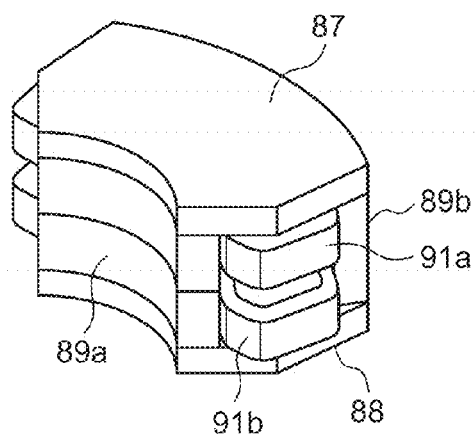
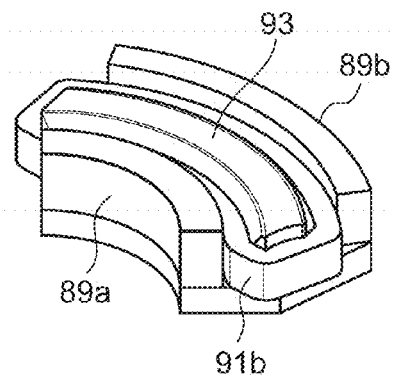


FIG.12A



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FIG.12B



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FIG.13

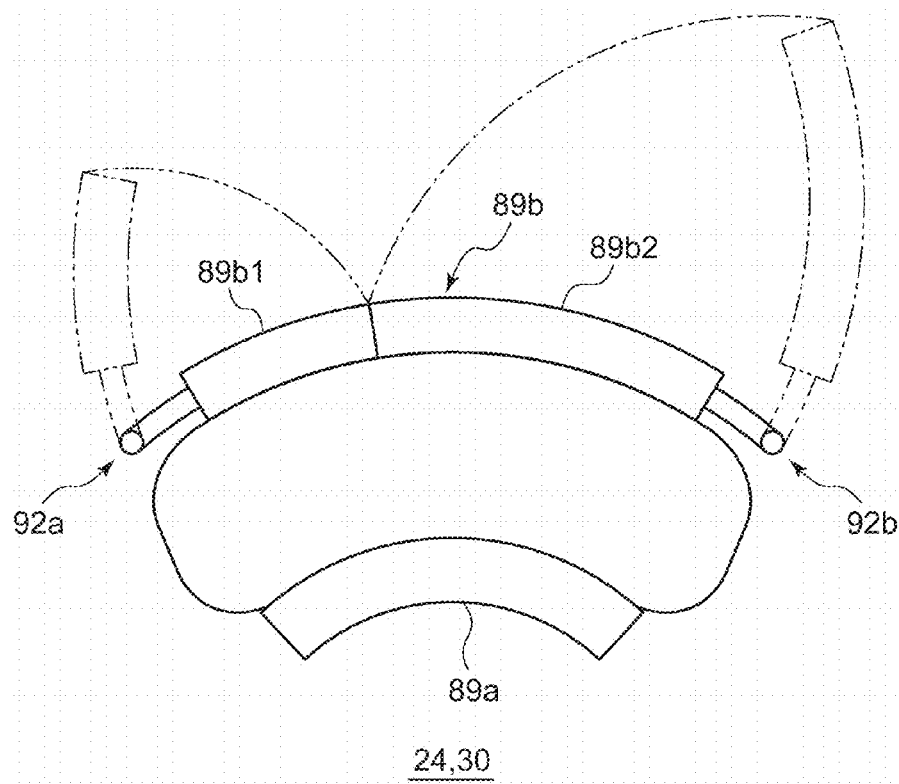


FIG. 14A

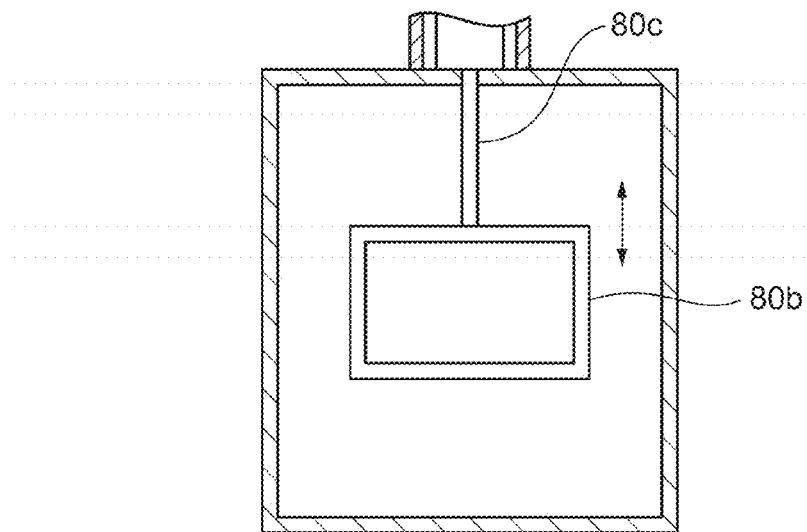


FIG. 14B

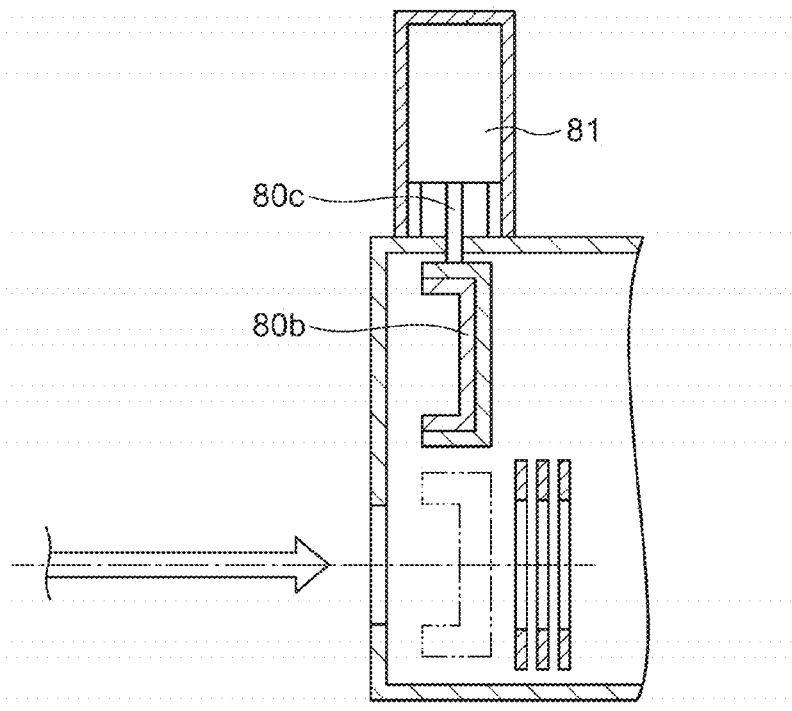




FIG.15

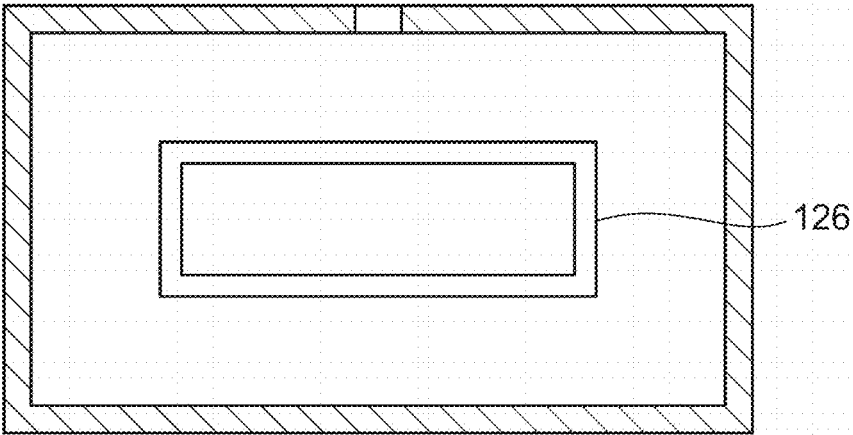
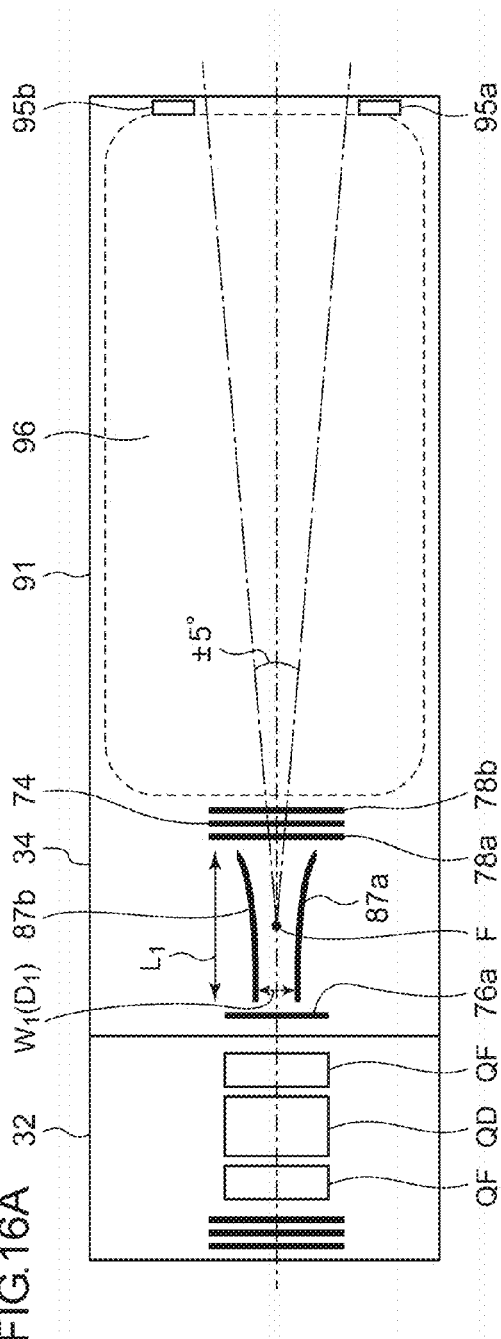


FIG. 16A



மேரீனா

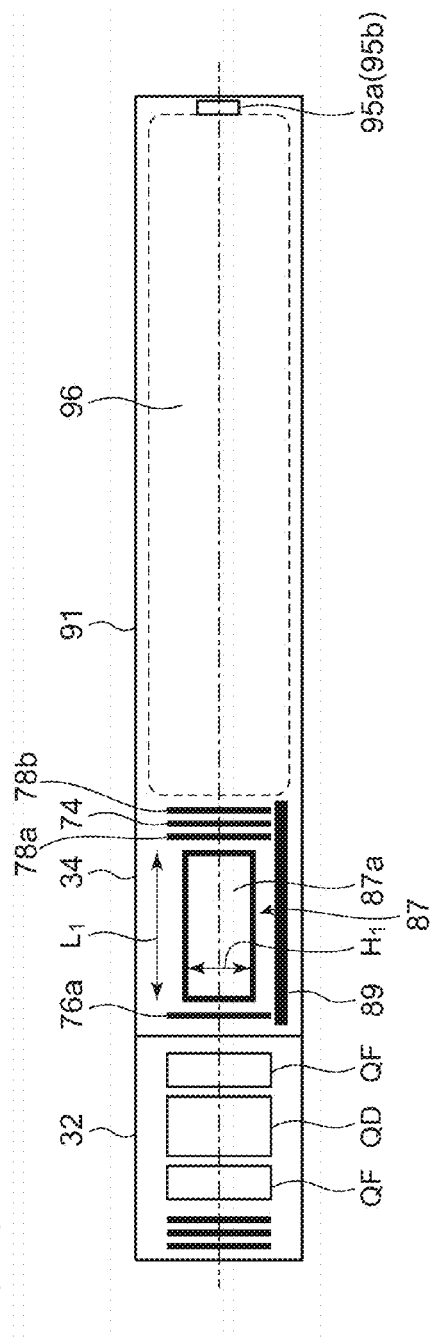


FIG.17

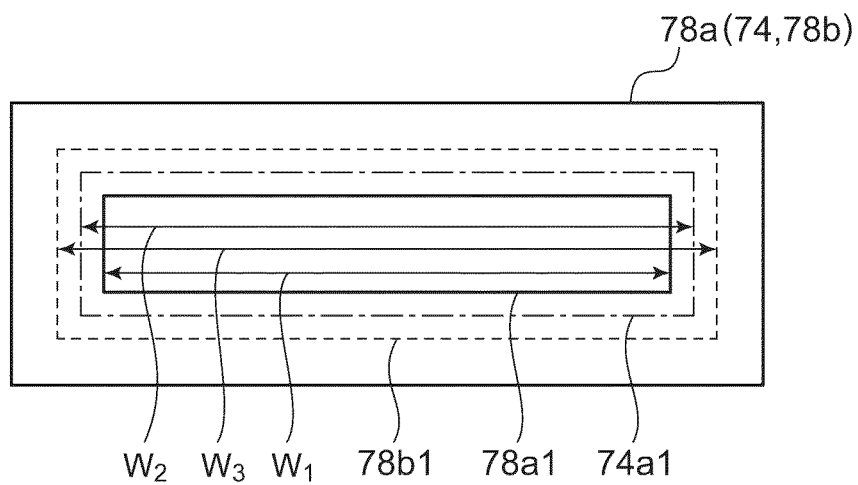


FIG.18

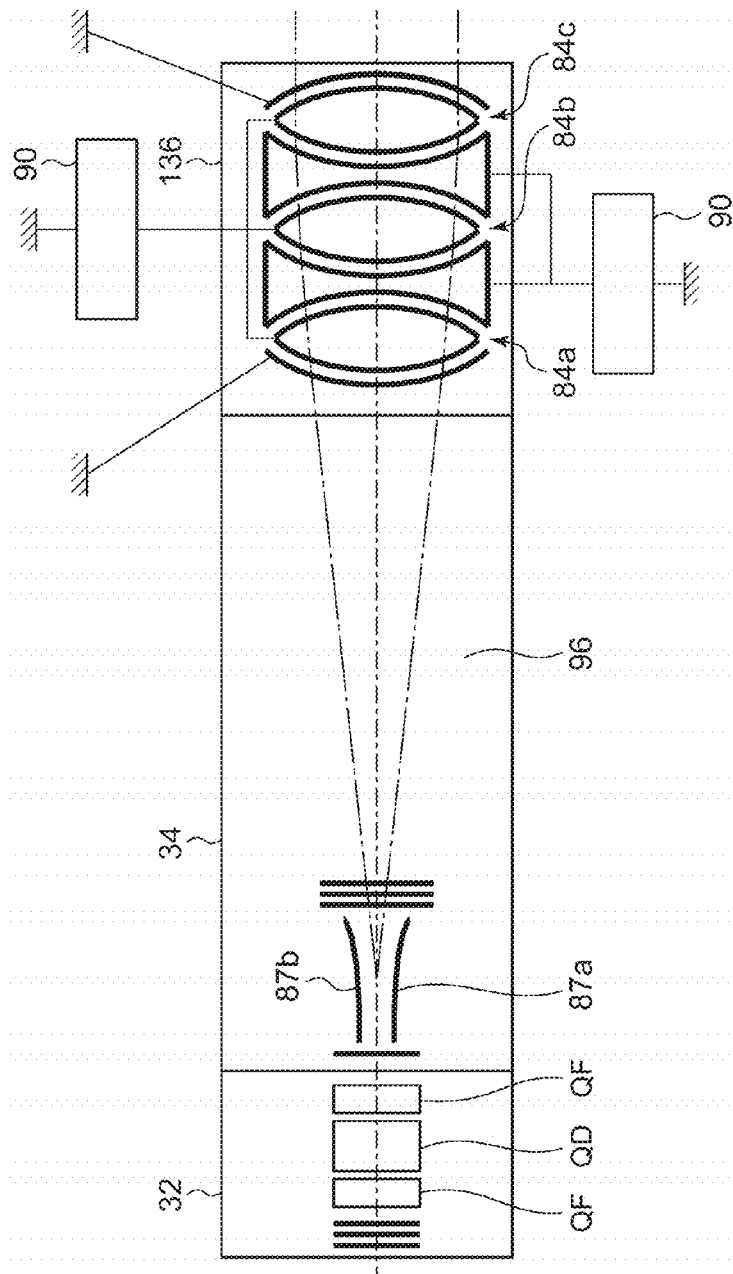


FIG. 19

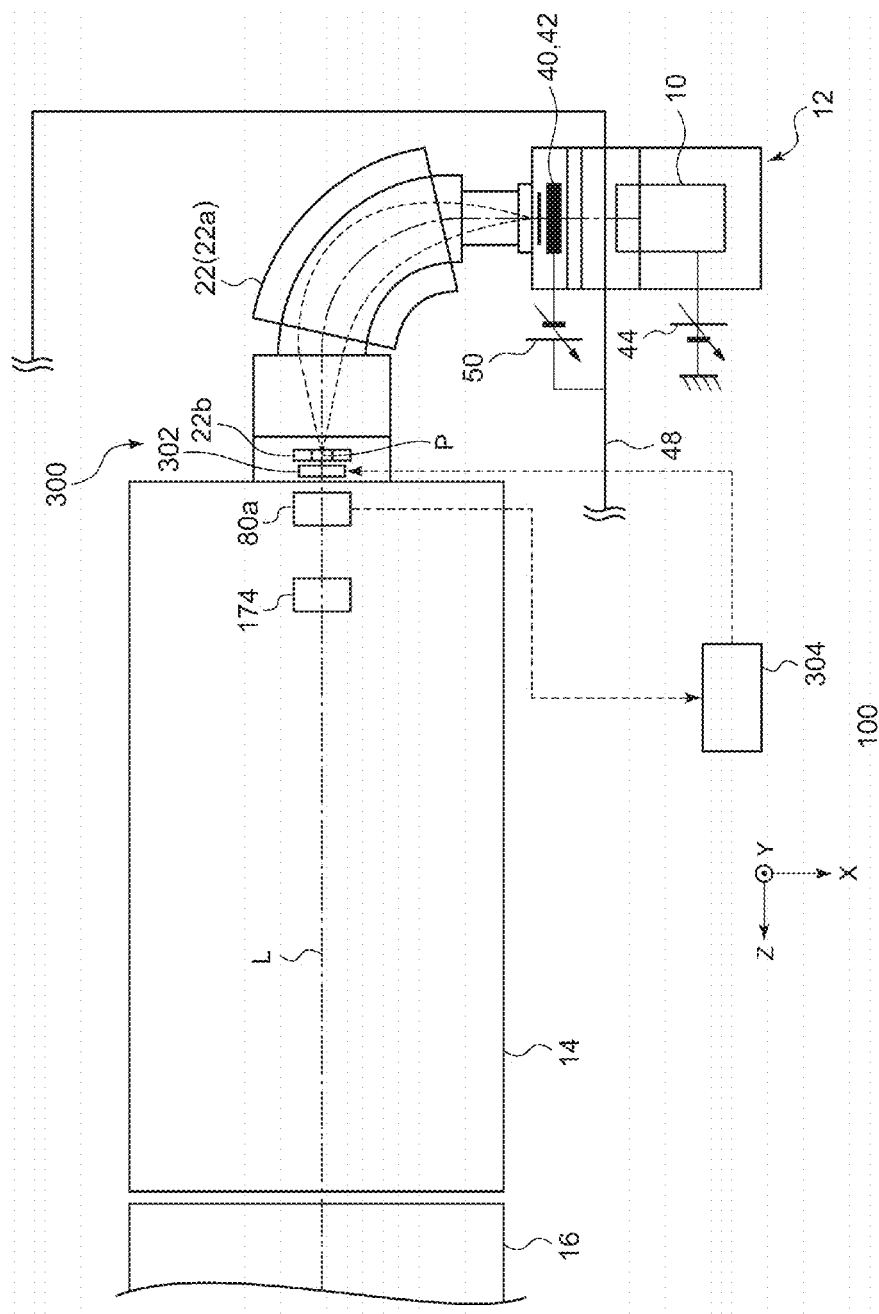


FIG.20

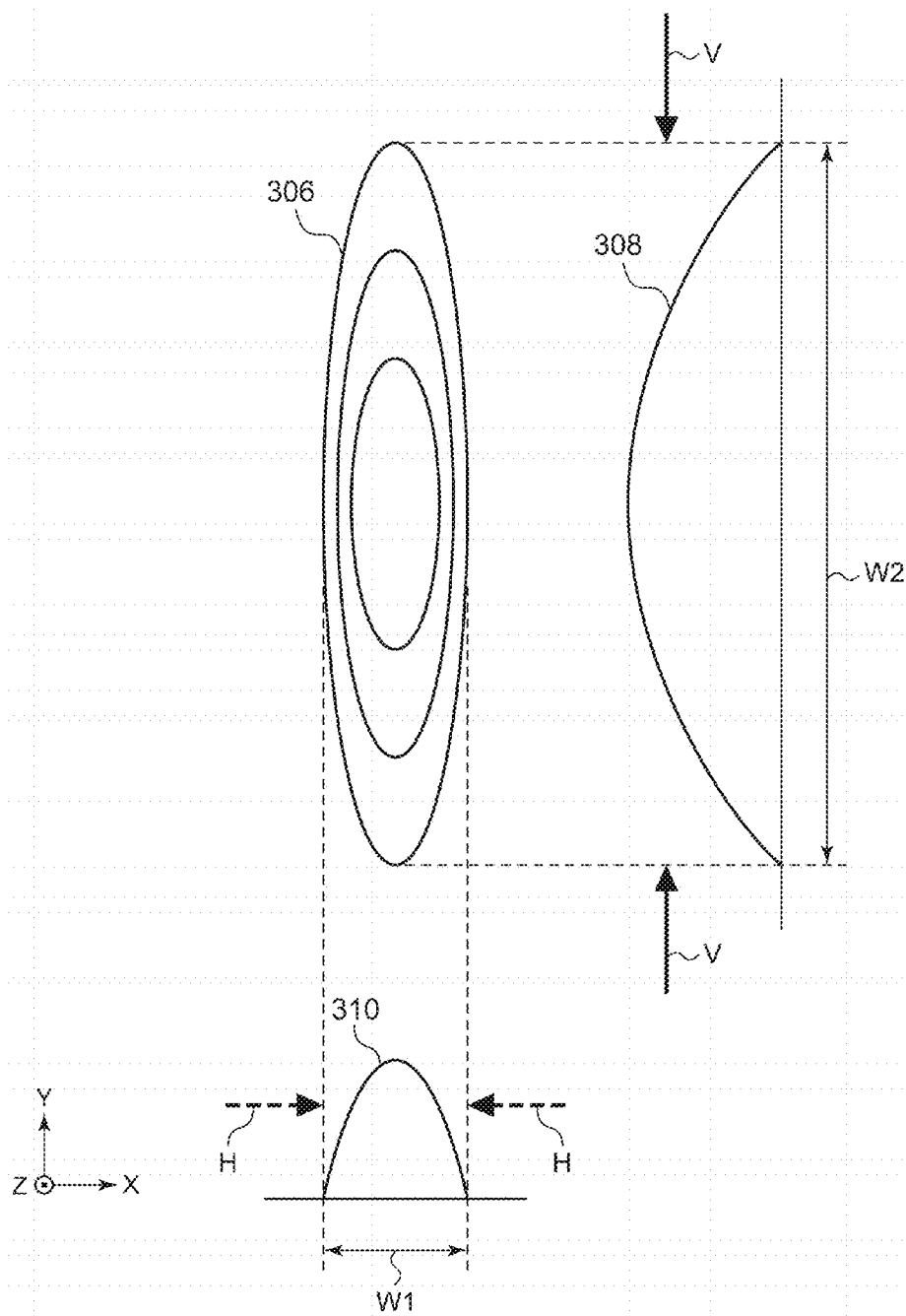


FIG.21A

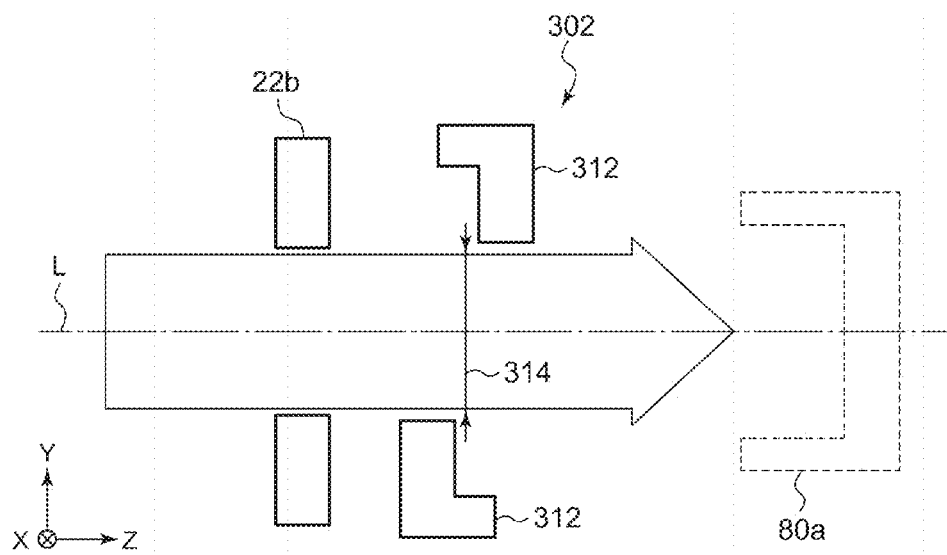
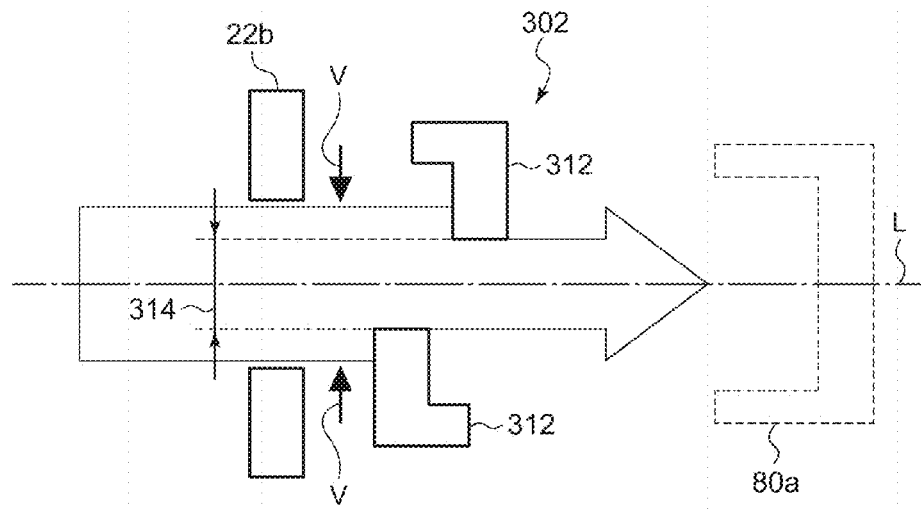
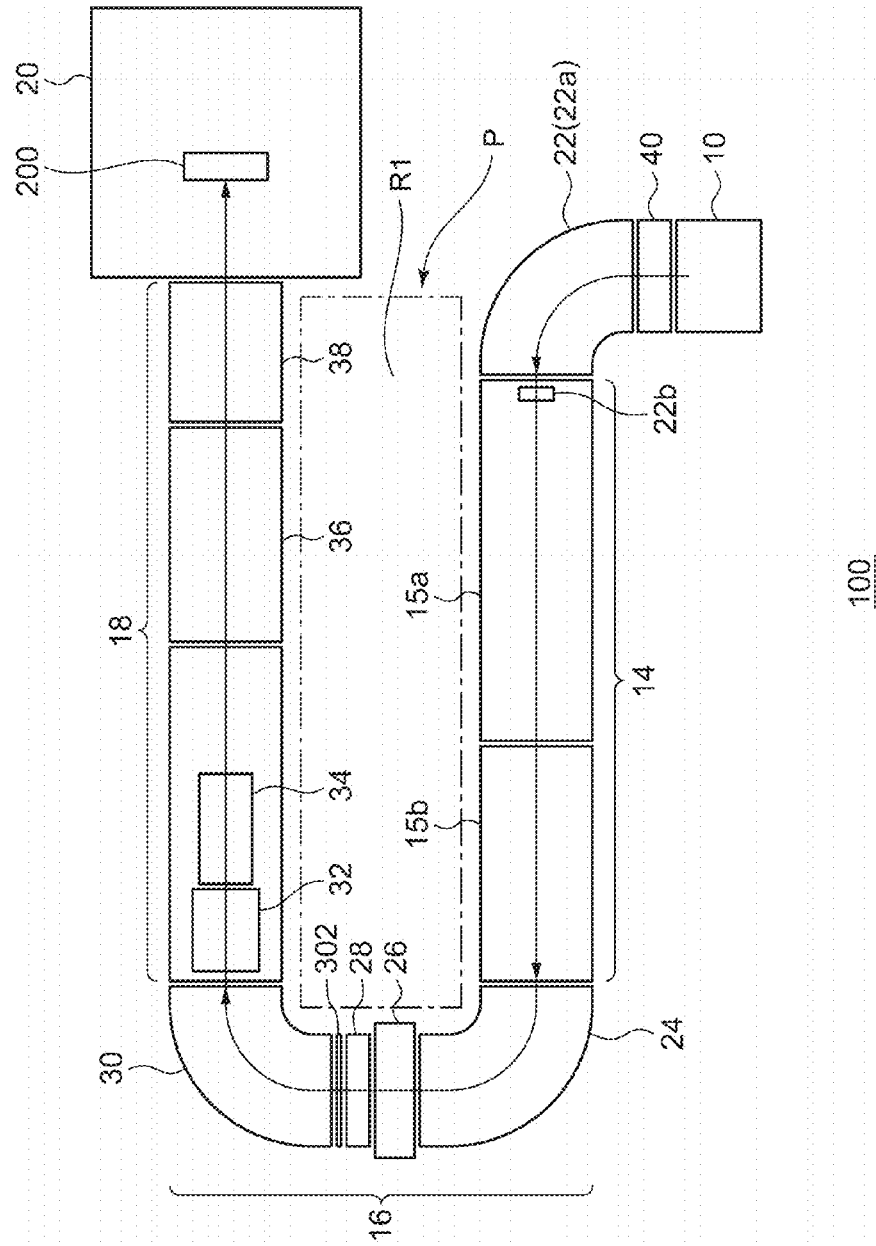


FIG.21B

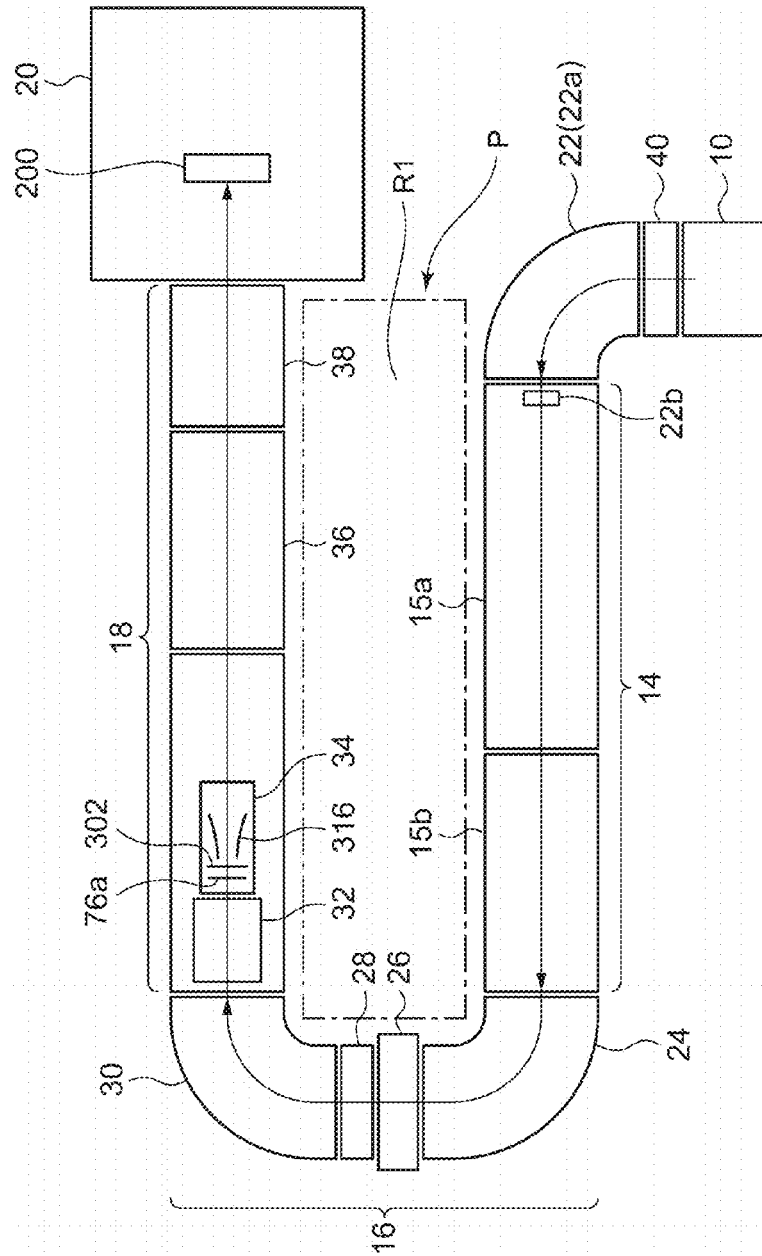


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# HIGH ENERGY ION IMPLANTER, BEAM CURRENT ADJUSTER, AND BEAM CURRENT ADJUSTMENT METHOD

## RELATED APPLICATION

Priority is claimed to Japanese Patent Application No. 2013-240647, filed on Nov. 21, 2013, the entire content of which is incorporated herein by reference.

## BACKGROUND OF THE INVENTION

### 1. Field of the Invention

The present invention relates to a high energy ion implanter.

### 2. Description of the Related Art

In a semiconductor device production process, an important process is generally performed in which ions are implanted into a semiconductor wafer in a vacuum state so as to add impurities to crystals of the semiconductor wafer. Accordingly, a conductive property is changed so that the semiconductor wafer becomes a semiconductor device. An apparatus used in this process is generally called an ion implanter that accelerates impurity atoms as ions for the semiconductor device and implants impurity atoms into the semiconductor wafer.

Hitherto, an apparatus for performing a high energy ion implantation by further deeply implanting an ion beam into the semiconductor wafer has been used with the high integration and the high performance of the semiconductor device. Such an apparatus is particularly called a high energy ion implanter. As an example, there is known a method of configuring an ion beam acceleration system by a tandem type electrostatic accelerator.

#### (Batch Type)

Further, a batch treatment type high energy ion implanter with a radio frequency linear accelerator for performing a radio frequency acceleration has been used for many years.

The batch treatment type ion implantation is a method of uniformly implanting ions into wafers while several tens of silicon wafers are loaded on the outer periphery of an aluminum disk having a diameter of about 1 m and the disk is rapidly rotated by 1000 revolutions per minute. In order to prevent the pop-out state of the wafer by a centrifugal force, the wafer loading portion of the disk has an angle of about 5° with respect to a rotation surface (a surface perpendicular to a rotation shaft). The batch treatment type ion implantation method has a problem in which an implantation angle (an angle at which the ions are incident to the wafer) is different by about 1° between the center and the end of the wafer (the implantation angle deviation) due to the above-described angle and the rotation of the wafer.

In general, a die on the wafer has an ion implantation performing region and a non-ion implantation performing region, and the non-ion implantation performing region is covered by an organic substance called a photoresist. Since the ions do not need to penetrate the photoresist during the implantation, the photoresist to be coated during the high energy ion implantation is much thickened. In the ion implantation performing region, the photoresist is excluded by lithography. However, when the integration degree is high and the implantation region is minute, the ions are perpendicularly implanted to a bottom of a deep hole surrounded by an upright photoresist wall. In the ion implantation in the structure having a high aspect ratio, the high precision of implantation angle is demanded.

In particular, in a case where a high-quality imaging device such as a CCD is produced, the resolution increases with the deep ion implantation, and hence the sensitivity is improved. For this reason, a super high energy ion implantation (3 to 8 MeV) is also performed. In this case, the allowed implantation angle error is about 0.1°, and a batch type apparatus with a large implantation angle deviation may not be used.

#### (Single Wafer Type High Energy Ion Implanter)

Therefore, a single wafer type high energy ion implanter has been practically realized in recent years. In the batch type, the ion beam is uniformly implanted in the horizontal direction in a manner such that the beam is fixed and the wafer moves (the rotation on the disk). On the contrary, in the single wafer type, the beam moves (so that the beam scans in the horizontal direction) and the wafer is fixed. In this type, when the scan beam is collimated, the implantation dose may be uniform within the wafer surface, and the implantation angle may be also uniform. Accordingly, the problem of the implantation angle deviation may be solved. Furthermore, the dose uniformity in the vertical direction is realized by moving the wafer at a constant velocity in both types, but the angle error does not occur in accordance with the movement.

In addition, since the single wafer type ion implanter does not uselessly consume the silicon wafer when a small number of wafers are treated, the single wafer type ion implanter is suitable for a small lot multi-product production, and hence a demand therefor has been increased in recent years.

Here, in the production of the high-quality imaging device, there is a need to meet various difficult demands in which the angle precision is needed, the metal contamination needs to be removed, the implantation damage (the residual crystal defect after the annealing) needs to be small, and the implantation depth precision (the energy precision) needs to be good. Accordingly, even the single wafer type ion implanter has many points to be improved.

In the single wafer type high energy ion implanter of the related art, the tandem type electrostatic accelerator or the radio frequency acceleration type heavy ion linac (the linear accelerator) has been used as the high energy acceleration type.

The downstream side of the acceleration system is provided with an energy filtering magnet, a beam scanner, and a parallelizing (parallelization) magnet that collimates a scan orbit by a magnetic field. Then, the beam has the same incident angle (implantation angle) with respect to the wafer at any scan position due to the parallelizing magnet. The ion energy is up to about 3 to 4 MeV.

Further, in a part of the (single wafer type) medium current ion implanter used in the energy region (10 to 600 keV) lower than that of the high energy ion implanter, an electric field parallel lens is used which collimates the scan orbit by the electric field (the electrode). Since the electric field parallel lens may collimate the scan orbit while keeping the symmetry of the orbit, the angle precision is more critically treated compared to the parallelizing magnet. Further, in this apparatus, an electric field type deflection electrode called an AEF (Angular Energy Filter) is attached to the vicinity of the wafer. Since the ions subjected to a change in charge state during the transportation of the beam or the particles generated in the beamline are removed by the AEF, a highly pure beam may be supplied.

## SUMMARY OF THE INVENTION

An exemplary object of an aspect of the present invention is to adjust an implanting beam current in a high energy ion implanter.

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According to an aspect of the invention, there is provided a high energy ion implanter including a high energy multistage linear acceleration unit. The high energy ion implanter further includes: a beamline component arranged upstream or downstream of the high energy multistage linear acceleration unit to form a focus point of an ion beam; and a variable aperture device disposed at the focus point or a vicinity thereof to adjust a beam width of the ion beam in a direction perpendicular to a focusing direction of the ion beam at the focus point in order to control an implanting beam current.

According to an aspect of the invention, there is provided a beam current adjuster for an ion implanter. The beam current adjuster includes a variable aperture device disposed at a focus point of the ion beam or a vicinity thereof to adjust a beam width of the ion beam in a direction perpendicular to a focusing direction of the ion beam at the focus point in order to control an implanting beam current.

According to an aspect of the invention, there is provided a beam current adjustment method for a high energy ion implanter with a high energy multistage linear acceleration unit. The method includes: focusing an ion beam at a focus point formed upstream or downstream of the high energy multistage linear acceleration unit; and adjusting a beam width of the ion beam in a direction perpendicular to a focusing direction of the ion beam by using a variable aperture device disposed at the focus point or a vicinity thereof in order to control an implanting beam current.

Optional combinations of the aforementioned constituting elements, and implementations of the invention in the form of methods, apparatuses, systems, computer programs and so forth may also be practiced as additional modes of the present invention.

## BRIEF DESCRIPTION OF THE DRAWINGS

Embodiments will now be described, by way of example only, with reference to the accompanying drawings which are meant to be exemplary, not limiting, and wherein like elements are numbered alike in several Figures, in which:

FIG. 1 is a schematic view illustrating a schematic layout and a beamline of a high energy ion implanter according to an embodiment;

FIG. 2A is a top view illustrating a schematic configuration of an ion beam generation unit, and FIG. 2B is a side view illustrating the schematic configuration of the ion beam generation unit;

FIG. 3 is a top view illustrating an entire layout including a schematic configuration of a high energy multistage linear acceleration unit;

FIG. 4 is a block diagram illustrating a configuration of a control system of a focusing/defocusing lens and the high energy multistage linear acceleration unit obtained by linearly arranging acceleration electric fields (gaps) of front ends of a plurality of radio frequency resonators;

FIGS. 5A and 5B are top views illustrating a schematic configuration of an EFM (an energy analyzing deflection electromagnet), an energy width confining slit, an energy analysis slit, a BM (a lateral center orbit correcting deflection electromagnet), a beam focusing/defocusing device, and a beam scanner (a scanner);

FIG. 6A is a top view illustrating a schematic configuration from a beam scanner to a substrate processing/supplying unit along a beamline after a beam collimator, and FIG. 6B is a side view illustrating a schematic configuration from a beam scanner to a substrate processing/supplying unit along a beamline after a beam collimator;

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FIG. 7 is a schematic top view illustrating a main part of an example of the beam scanner;

FIG. 8 is a schematic side view illustrating a main part of an example of the beam scanner;

FIG. 9 is a schematic front view illustrating a structure in which an example of the beam scanner is removably attached to a halfway position of an ion beamline path when viewed from the downstream side;

FIG. 10 is a schematic view illustrating another aspect of a deflection electrode of an angle energy filter;

FIG. 11A is a schematic top view illustrating a quadrupole lens as a lateral focusing lens, and FIG. 11B is a schematic front view illustrating the quadrupole lens;

FIGS. 12A and 12B are perspective views illustrating an example of a configuration of an electromagnet;

FIG. 13 is a schematic view illustrating an opening and closing portion included in the electromagnet;

FIG. 14A is a schematic front view illustrating a resolver-faraday cup having substantially the same configuration as that of an injector faraday cup, and FIG. 14B is a schematic view illustrating an operation of the resolver-faraday cup;

FIG. 15 is a schematic front view illustrating a lateral elongated faraday cup;

FIG. 16A is a top view illustrating a schematic configuration from a beam focusing/defocusing device to a beam scanner according to the embodiment, and FIG. 16B is a side view illustrating a schematic configuration from the beam focusing/defocusing device to the beam scanner according to the embodiment;

FIG. 17 is a schematic view illustrating a relation in size among an opening width of a downstream ground electrode, an opening width of a suppression electrode, and an opening width of an upstream ground electrode;

FIG. 18 is a schematic view illustrating another example of the beam collimator.

FIG. 19 is a schematic view illustrating a beam current adjuster according to an embodiment of the invention;

FIG. 20 is a view illustrating an ion beam cross-section at an ion beam focus point;

FIGS. 21A and 21B are schematic views illustrating a variable aperture device according to an embodiment of the invention;

FIG. 22 is a schematic view illustrating the arrangement of a beam current adjuster according to another embodiment of the invention; and

FIG. 23 is a schematic view illustrating the arrangement of a beam current adjuster according to a further embodiment of the invention.

## DETAILED DESCRIPTION OF THE INVENTION

The invention will now be described by reference to the preferred embodiments. This does not intend to limit the scope of the present invention, but to exemplify the invention.

Hereinafter, an example of a high energy ion implanter according to the embodiment will be described in detail. First, the reason why the invention is contrived by the present inventor and the like will be described.

(Parallel Magnet)

The following problems arise in a high energy ion implanter of the related art that employs a parallel (collimate) magnet which parallelizes (collimates) an orbit by a deflection magnetic field.

When a high energy ion is implanted into a photoresist-coated wafer, a large amount of an outgas is generated. Then, an interaction occurs between molecules of the outgas and beam ions, and hence the charge state of some ions change.

When a change in valance occurs while the beam passes through the parallelizing magnet, a deflection angle changes and the parallelism of the beam is collapsed. Accordingly, an implantation angle with respect to the wafer is not uniform.

Further, the amount (the number or the dose) of the implanted ions may be obtained by measuring a beam current value in a faraday cup disposed near the wafer. However, the measurement value is influenced due to a change in charge state, and hence the measurement value is deviated from a predetermined implantation dose. As a result, the expected characteristics of a semiconductor device may not be obtained.

Further, in the parallelism of one parallel magnet, the inner and outer orbits have different deflection angles and different orbit lengths. For this reason, the ratio of the ions subjected to a change in charge state increases as it goes toward the outer orbit, and hence the dose uniformity inside the wafer surface is also degraded.

Thus, a recent demand for highly precise implantation may not be sufficiently handled by the beam transportation type of the high energy ion implanter of the related art.

Further, the parallelizing magnet needs a wide magnetic pole in the scan direction and a parallelizing section having a certain length. Since the length and the size of the magnetic pole increase when the energy increases, the weight of the parallelizing magnet considerably increases. In order to stably fix and hold the apparatus, the design for the strength of the semiconductor factory needs to be reinforced, and the power consumption considerably increases.

These problems may be solved when the electric field collimating lens and the electric field (the electrode type) energy filter (AEF: Angular Energy Filter) used in the above-described medium current ion implanter may be used in the high energy region. The electric field collimating lens aligns and collimates the scan orbit to the center orbit while keeping the symmetry of the orbit, and the AEF removes the ions subjected to a change in charge state directly before the wafer. Accordingly, even when a large amount of the outgas exists, a beam without an energy contamination may be obtained, and hence the implantation angle in the scan direction does not become non-uniform as in the case of the parallelizing magnet. As a result, the ions may be implanted with an accurate implantation distribution in the depth direction and a uniform implantation dose, and the implantation angle also becomes uniform, thereby realizing a highly precise ion implantation. Further, since the light-weight electrode member is used, the power consumption may be decreased compared to the electromagnet.

The point of the invention is to obtain an apparatus capable of performing the same highly precise implantation as that of the medium current apparatus in the high energy apparatus by introducing an excellent system of the medium current ion implanter into the high energy ion implanter. The problems to be solved in this trial will be described below. The first problem is the length of the apparatus.

In a case where the ion beams are deflected at the same trajectory, the necessary magnetic field is proportional to the square root of the energy, and the necessary electric field is proportional to the energy. Thus, the length of the deflection magnetic pole is proportional to the square root of the energy, and the length of the deflection electrode is proportional to the energy. When the highly precise angle implantation is tried by mounting the electric field collimating lens and the electric field AEF onto the high energy ion implanter, the beam transportation system (the distance from the scanner to the wafer) largely increases in length compared to the apparatus of the related art that uses the parallelizing magnet.

For example, as the high energy ion implanter that includes a parallelization mechanism using such an electric field, a structure is considered which is obtained by substantially linearly fixing constituents such as an ion source, an amass analysis magnet, a tandem type electrostatic accelerator or a radio frequency linear accelerator, a beam scanner, a scan orbit parallelization device, an energy filter, an implantation process chamber, and a substrate transportation unit (an end station) as in the case of the high energy ion implanter of the related art. In this case, the entire length of the apparatus increase by about 20 m compared to the apparatus of the related art having a length of about 8 m. Accordingly, it takes large effort when the installation place is set and prepared and the installation operation is performed, and then the installation area also increases. Further, a work space is also needed for the alignment adjustment of the devices and the maintenance, the repair, or the adjustment thereof after the operation of the apparatus. Such a large ion implanter may not satisfy a demand for adjusting the size of the apparatus in the semiconductor production line to the actual size of the apparatus arranged in the factory production line.

In view of such circumstances, an object of the beamline structure in the aspect of the invention is to provide a highly precise high energy ion implanter with an electric field collimating lens and an electric field energy filter by simplifying and efficiently adjusting an installation place setting and preparing work, an installation work, or a maintenance work while ensuring a sufficient work area and realizing a technique of suppressing an increase in installation area.

(U-Shaped Folded Beamline)

The object may be attained by a configuration in which the beamline of the high energy ion implanter includes a long line portion that is formed by a plurality of units for accelerating an ion beam generated by an ion source and a long line portion that is formed by a plurality of units for adjusting and implanting a scan beam into a wafer and a horizontal U-shaped folded beamline having the long line portions facing each other is formed. Such a layout is realized by substantially matching the length of the beam transportation unit including a beam scanner, a beam collimator, an energy filter, and the like to the length of the unit accelerating the ions from the ion source. Then, a sufficiently wide space is provided between two long line portions for the maintenance work.

An aspect of the invention is supposed based on the layout of the beamline, and an object thereof is to provide a high energy ion implanter capable of scanning a high energy ion beam in a range sufficiently wider than a wafer size, instantly stopping a transportation in the event of a beam transportation failure, and normally maintaining a highly precise implantation state by scanning a high energy beam with satisfactory responsiveness.

A high energy ion implanter according to an aspect of the invention accelerates ions generated by an ion source so as to generate an ion beam, transports the ion beam to a wafer along a beamline, and implants the ion beam into a wafer, and includes: a beam generation unit that includes an ion source and amass analyzer; a high energy multistage linear acceleration unit that accelerates an ion beam so as to generate a high energy ion beam; a high energy beam deflection unit that changes the direction of the high energy ion beam toward the wafer; a beam transportation unit that transports the deflected high energy ion beam to the wafer; and a substrate processing/supplying unit that uniformly implants the transported high energy ion beam into the semiconductor wafer. The beam transportation unit includes a beam focusing/defocusing device, a high energy beam scanner, a high energy electric field type beam collimator, and a high energy electric field

type final energy filter. Then, the high energy ion beam emitted from the deflection unit is scanned and collimated by the beam scanner and the electric field type beam collimator, mixed ions having a different mass, a different ion charge state, and different energy are removed by the high energy electric field type final energy filter, and the resultant ions are implanted into the wafer.

In this configuration, the high energy beam scanner is configured as an electric field type beam scanner that is operated in a finely adjustable triangular wave. The electric field type having fast responsiveness is employed. When a discharge or the like occurs during the ion implantation, the beam becomes instable. Accordingly, in a case where the non-uniformity of the implantation dose is predicted, a system may be obtained which instantly stops the implantation and immediately resumes the implantation in a stabilized state. Thus, the implantation precision may be ensured in any case. Further, since the operation frequency may be easily changed, the amount of the crystal defect occurring in the silicon crystals during the ion implantation may be controlled, and hence the quality of the product may be improved.

The electric field type beam scanner includes a pair of deflection electrodes, but an extremely high voltage may not be applied to the electrodes for the fast responsiveness. However, in order to perform the highly precise implantation that keeps the implantation dose non-uniformity of the entire wafer surface at 0.5% or less, the scan range needs to be sufficiently wider than the wafer size. For this reason, the beam scanner needs to have a sufficient deflection angle with respect to the high energy beam. Therefore, in the invention, a sufficient deflection angle is obtained in a manner such that a relation of  $L_1 \geq 5D_1$  is satisfied when the gap between the pair of deflection electrodes is indicated by  $D_1$  and the length thereof in the beam traveling direction is indicated by  $L_1$ .

According to the aspect of the invention, the high energy ion beam may be scanned in a range sufficiently wider than the wafer size, and hence the highly precise implantation in which the implantation dose non-uniformity of the entire wafer surface is suppressed to 0.5% or less may be performed. Further, when a problem such as the discharge of the electrode occurs during the transportation of the beam, the high energy beam scanning operation having satisfactory responsiveness and instantly stopping the ion implantation may be performed. Accordingly, the highly precise implantation may be maintained.

Therefore, the high energy ion implanter according to the aspect of the embodiment is an ion implanter that accelerates the ions generated by the ion source, transports the ions as the ion beam along the beamline to the wafer, and implants the ions into the wafer. This apparatus includes the high energy multistage linear acceleration unit that accelerates the ion beam so as to generate the high energy ion beam, the deflection unit that changes the direction of the orbit of the high energy ion beam toward the wafer, and the beam transportation unit that transports the deflected high energy ion beam to the wafer, and the collimated ion beam is highly precisely irradiated to the wafer moving in a mechanical scan state so as to be implanted into the wafer.

The high energy ion beam that is emitted from the radio frequency (AC-type) high energy multistage linear acceleration unit for highly accelerating the ion beam includes a certain range of energy distribution. For this reason, in order to scan and collimate the high energy ion beam of the rear stage and irradiate the high energy ion beam to the wafer moving in a mechanical scan state, there is a need to perform the highly precise energy analysis, the center orbit correction, and the beam focusing/defocusing adjustment in advance.

The beam deflection unit includes at least two highly precise deflection electromagnets, at least one energy width confining slit, an energy analysis slit, and at least one lateral focusing unit. The plurality of deflection electromagnets are formed so as to perform the energy analysis of the high energy ion beam, the precise correction of the ion implantation angle, and the suppression of the energy dispersion. In the highly precise deflection electromagnets, a nuclear magnetic resonance probe and a hall probe are attached to the electromagnet for the energy analysis, and only the hall probe is attached to the other electromagnet. The nuclear magnetic resonance probe is used to calibrate the hall probe, and the hall probe is used for the uniform magnetic field feedback control.

The beam transportation unit may implant ions by scanning and parallelizing the high energy ion beam and highly precisely irradiating the high energy ion beam to the wafer moving in a mechanical scan state.

Hereinafter, an example of the high energy ion implanter according to the embodiment will be described in more detail with reference to the drawings. Furthermore, the same reference numerals will be given to the same components in the description of the drawings, and the repetitive description of the same components will be appropriately omitted. Further, the configuration mentioned below is merely an example, and does not limit the scope of the invention.

#### (High Energy Ion Implanter)

First, a configuration of the high energy ion implanter according to the embodiment will be simply described. Furthermore, the content of the specification may be applied to not only the ion beam as one of kinds of charged particles, but also the apparatus involved with the charged particle beam.

FIG. 1 is a schematic view illustrating a schematic layout and a beamline of a high energy ion implanter **100** according to the embodiment.

The high energy ion implanter **100** according to the embodiment is an ion implanter that includes a radio frequency linear acceleration type ion accelerator and a high energy ion transportation beamline, and is configured to accelerate ions generated by an ion source **10**, transports the ions along the beamline to a wafer (a substrate) **200** as an ion beam, and implants the ions into a wafer **200**.

As illustrated in FIG. 1, the high energy ion implanter **100** includes an ion beam generation unit **12** that generates ions and separates the ions by mass, a high energy multistage linear acceleration unit **14** that accelerates an ion beam so as to become a high energy ion beam, a beam deflection unit **16** that performs an energy analysis, a center orbit correction, and an energy dispersion control on the high energy ion beam, a beam transportation line unit **18** that transports the analyzed high energy ion beam to a wafer, and a substrate processing/supplying unit **20** that uniformly implant the transported high energy ion beam into the semiconductor wafer.

The ion beam generation unit **12** includes the ion source **10**, an extraction electrode **40**, and a mass analyzer **22**. In the ion beam generation unit **12**, a beam is extracted from the ion source **10** through the extraction electrode and is accelerated, and the extracted and accelerated beam is subjected to a mass analysis by the mass analyzer **22**. The mass analyzer **22** includes a mass analysis magnet **22a** and a mass analysis slit **22b**. There is a case in which the mass analysis slit **22b** is disposed directly behind the mass analysis magnet **22a**. However, in the embodiment, the mass analysis slit is disposed inside the entrance of the high energy multistage linear acceleration unit **14** as the next configuration.

Only the ions necessary for the implantation are selected as a result of the mass analysis using the mass analyzer **22**, and the ion beam of the selected ions is led to the next high energy

multistage linear acceleration unit **14**. The direction of the ion beam that is further accelerated by the high energy multistage linear acceleration unit **14** is changed by the beam deflection unit **16**.

The beam deflection unit **16** includes an energy analysis electromagnet **24**, a lateral focusing quadrupole lens **26** that suppresses an energy dispersion, an energy width confining slit **27** (see FIGS. **5A** and **5B** below), an energy analysis slit **28**, and a deflection electromagnet **30** having a steering function. Furthermore, the energy analysis electromagnet **24** may be called an energy filter electromagnet (EFM). The direction of the high energy ion beam is changed by the deflection unit so as to be directed toward the substrate wafer.

The beam transportation line unit **18** is used to transport the ion beam emitted from the beam deflection unit **16**, and includes a beam focusing/defocusing device **32** formed by a focusing/defocusing lens group, a beam scanner **34**, a beam collimator **36**, and a final energy filter **38** (with a final energy separation slit). The length of the beam transportation line unit **18** is designed so as to match the lengths of the ion beam generation unit **12** and the high energy multistage linear acceleration unit **14**, and the beam transportation line unit **18** is connected to the beam deflection unit **16** so as to form a U-shaped layout as a whole.

The substrate processing/supplying unit **20** is provided at the termination end of the downstream side of the beam transportation line unit **18**, and the implantation process chamber accommodates a beam monitor that measures the beam current, the position, the implantation angle, the convergence/divergence angle, the vertical and horizontal ion distribution, and the like of the ion beam, a charge prevention device that prevents the charge of the substrate by the ion beam, a wafer transportation mechanism that carries the wafer (the substrate) **200** and installs the wafer at an appropriate position and an appropriate angle, an ESC (Electro Static Chuck) that holds the wafer during the ion implantation, and a wafer scan mechanism that operates the wafer in a direction perpendicular to the beam scan direction at the velocity in response to a change in the implantation beam current.

In this way, the high energy ion implanter **100** that is formed by arranging the units in a U-shape ensures satisfactory workability while suppressing an increase in footprint. Further, in the high energy ion implanter **100**, the units or the devices are formed as a module, and hence may be attached, detached, and assembled in accordance with the beamline reference position.

Next, the units and the devices constituting the high energy ion implanter **100** will be described further in detail.

(Ion Beam Generation Unit)

FIG. **2A** is a top view illustrating a schematic configuration of the ion beam generation unit, and FIG. **2B** is a side view illustrating a schematic configuration of the ion beam generation unit.

As illustrated in FIGS. **2A** and **2B**, the extraction electrode **40** that extracts an ion beam from plasma generated inside an ion chamber (an arc chamber) is provided at the exit of the ion source **10** disposed at the most upstream side of the beamline. An extraction suppression electrode **42** that suppresses electrons included in the ion beam extracted from the extraction electrode **40** from reversely flowing toward the extraction electrode **40** is provided near the downstream side of the extraction electrode **40**.

The ion source **10** is connected to an ion source high-voltage power supply **44**. An extraction power supply **50** is connected between the extraction electrode **40** and a terminal **48**. The downstream side of the extraction electrode **40** is

provided with the mass analyzer **22** that separates predetermined ions from the incident ion beam and extracts the separated ion beam.

As illustrated in FIGS. **5A** and **5B** to be described below, a faraday cup (for an injector) **80a** that measures the total beam current of the ion beam is disposed at the foremost portion inside the linear acceleration portion housing of the high energy multistage linear acceleration unit **14**.

FIG. **14A** is a schematic front view illustrating a resolver-faraday cup **80b** having substantially the same configuration as that of the injector faraday cup **80a**, and FIG. **14B** is a schematic view illustrating an operation of the resolver-faraday cup **80b**.

The injector faraday cup **80a** may be extracted from the vertical direction on the beamline by a driving mechanism, and is formed so that an opening faces the upstream side of the beamline while having a rectangular square shape in the horizontal direction. Accordingly, the injector faraday cup is used to completely interrupt the ion beam reaching the downstream side of the beamline on the beamline if necessary other than the function of measuring the total beam current of the ion beam during the adjustment of the ion source or the mass analysis electromagnet. Further, as described above, the mass analysis slit **22b** is disposed inside the entrance of the high energy multistage linear acceleration unit **14** directly before the injector faraday cup **80a**. Further, the width of the slit may be constant or variable. If the width of the slit is variable, the width may be adjusted in accordance with ion mass. The varying method of the width may be continuous, stepwise or switching a plurality of slits having different widths.

(High Energy Multistage Linear Acceleration Unit)

FIG. **3** is a top view illustrating the entire layout including the schematic configuration of the high energy multistage linear acceleration unit **14**. The high energy multistage linear acceleration unit **14** includes a plurality of linear accelerators for accelerating the ion beam, that is, an acceleration gap that interposes one or more radio frequency resonators **14a**. The high energy multistage linear acceleration unit **14** may accelerate the ions by the action of the radio frequency (RF) electric field. In FIG. **3**, the high energy multistage linear acceleration unit **14** includes a first linear accelerator **15a** that includes a basic multistage radio frequency resonator **14a** for a high energy ion implantation and a second linear accelerator **15b** that includes an additional multistage radio frequency resonator **14a** for a super high energy ion implantation.

Meanwhile, in the ion implanter that uses the acceleration of the radio frequency (RF), the amplitude  $V$  [kV] and the frequency  $f$  [Hz] of the voltage need to be considered as the parameter of the radio frequency. Further, in a case where a multistage radio frequency acceleration is performed, the phase  $\phi$  [deg] of the radio frequency is added as the parameter. In addition, a magnetic field lens (for example, a quadrupole electromagnet) or an electric field lens (for example, an electrostatic quadrupole electrode) is needed so as to control the expansion of the ion beam in the vertical and horizontal directions during or after the acceleration by the focusing/defocusing effect. Then, the optimal values of these operation parameters are changed by the ion energy passing there-through, and the strength of the acceleration electric field influences the focusing/defocusing action. For this reason, these values are determined after the parameter of the radio frequency is determined.

FIG. **4** is a block diagram illustrating a configuration of a control system of the focusing/defocusing lens and the high energy multistage linear acceleration unit obtained by linearly arranging the acceleration electric fields (the gaps) at the front ends of the plurality of radio frequency resonators.

The high energy multistage linear acceleration unit **14** includes one or more radio frequency resonators **14a**. As the components necessary for the control of the high energy multistage linear acceleration unit **14**, an input device **52** for allowing an operator to input a necessary condition, a control calculation device **54** that numerically calculates various parameters from the input condition and controls the components, an amplitude control device **56** that adjusts the voltage amplitude of the radio frequency, a phase control device **58** that adjusts the phase of the radio frequency, a frequency control device **60** that controls the frequency of the radio frequency, a radio frequency power supply **62**, a focusing/defocusing lens power supply **66** for a focusing/defocusing lens **64**, a display device **68** that displays an operation parameter thereon, and a storage device **70** that stores the determined parameter are needed. Further, the control calculation device **54** stores therein a numerical calculation code (a program) for numerically calculating various parameter in advance.

In the control calculation device **54** of the radio frequency linear accelerator, radio frequency parameters (an amplitude, a frequency, and a phase of a voltage) are calculated so as to obtain the optimal transportation efficiency by simulating the acceleration, the focusing, and the defocusing of the ion beam based on the input condition and the numerical calculation code stored therein. Also, the parameter (a Q coil current or a Q electrode voltage) of the focusing/defocusing lens **64** that is used to efficiently transport the ion beam is also calculated. The calculated various parameters are displayed on the display device **68**. The display device **68** displays a non-answerable mark for the acceleration condition that exceeds the ability of the high energy multistage linear acceleration unit **14**.

The voltage amplitude parameter is transmitted from the control calculation device **54** to the amplitude control device **56**, and the amplitude control device **56** adjusts the amplitude of the radio frequency power supply **62**. The phase parameter is transmitted to the phase control device **58**, and the phase control device **58** adjusts the phase of the radio frequency power supply **62**. The frequency parameter is transmitted to the frequency control device **60**. The frequency control device **60** controls the output frequency of the radio frequency power supply **62**, and controls the resonance frequency of the radio frequency resonator **14a** of the high energy multistage linear acceleration unit **14**. Further, the control calculation device **54** controls the focusing/defocusing lens power supply **66** by the calculated focusing/defocusing lens parameter.

The focusing/defocusing lens **64** that is used to efficiently transport the ion beam is disposed as many as needed at a position inside the radio frequency linear accelerator or a position before and behind the radio frequency linear accelerator. That is, the defocusing lens and the focusing lens are alternately provided at the position before and behind the acceleration gap of the front end of the multistage radio frequency resonator **14a**. At one side thereof, an additional longitudinal focusing lens **64b** (see FIGS. **5A** and **5B**) is disposed behind the lateral focusing lens **64a** (see FIGS. **5A** and **5B**) at the termination end of the second linear accelerator **15b**, adjusts the focusing and the defocusing of the high energy acceleration ion beam passing through the high energy multistage linear acceleration unit **14**, and causes the ion beam having an optimal two-dimensional beam profile to be incident to the beam deflection unit **16** of the rear stage.

In the direction of the electric field generated in the acceleration gap of the radio frequency linear accelerator, the ion acceleration direction and the ion deceleration direction

change at every several tens of nano seconds. In order to accelerate the ion beam to the high energy, the electric field needs to be directed in the acceleration direction when the ions enter all acceleration gaps which exist at several tens of places. The ions that are accelerated by a certain acceleration gap need to pass through a space (a drift space) in which the electric field between two acceleration gaps is shielded until the electric field of the next acceleration gap is directed in the acceleration direction. Since the ions are decelerated even at the early timing or the late timing, the ions may not reach the high energy. Further, since it is a very strict condition that the ions are carried along the acceleration phase in all acceleration gaps, the ion beam that reaches the predetermined energy is a resultant obtained from a difficult selection for the mass, the energy, and the charge (factors for determining the velocity) by the radio frequency linear accelerator. In this meaning, the radio frequency linear accelerator is also a good velocity filter.

(Beam Deflection Unit)

As illustrated in FIG. **1**, the beam deflection unit **16** includes the energy analysis electromagnet **24** as the energy filter deflection electromagnet (EFM), the energy width confining slit **27** (see FIGS. **5A** and **5B**), the energy analysis slit **28**, the lateral focusing quadrupole lens **26** that controls the energy dispersion at the wafer position, and the deflection electromagnet **30** that has an implantation angle correction function.

FIGS. **5A** and **5B** are top views illustrating a schematic configuration of the EFM (the energy analyzing deflection electromagnet), the energy width confining slit, the energy analysis slit, the BM (the lateral center orbit correcting deflection electromagnet), the beam focusing/defocusing device, and the beam scanner (the scanner). Furthermore, the sign L illustrated in FIG. **5A** indicates the center orbit of the ion beam.

The ion beam that passes through the high energy multistage linear acceleration unit **14** enables the energy distribution by a synchrotron oscillation. Further, there is a case in which the beam having a center value slightly deviated from the predetermined energy may be emitted from the high energy multistage linear acceleration unit **14** when the acceleration phase adjustment amount is large. Therefore, the magnetic field of the energy filter deflection magnet (EFM) is set so that only the ions having desired energy may pass by the beam deflection unit **16** to be described later, and a part of the beam selectively passes by the energy width confining slit **27** and the energy analysis slit **28**, so that the ion energy is adjusted to the setting value. The energy width of the passing ion beam may be set in advance by the horizontal opening widths of the energy width confining slit and the analysis slit. Only the ions passing through the energy analysis slit are led to the beamline of the rear stage, and are implanted into the wafer.

When the ion beam having the energy distribution is incident to the energy filter electromagnet (EFM) of which the magnetic field is controlled to a uniform value by the above-described feedback loop control system, the entire incident ion beam causes the energy dispersion while being deflected along the designed orbit, and the ions within a desired energy width range pass through the energy width confining slit **27** provided near the exit of the EFM. At the position, the energy dispersion increases to the maximum value, and the beam size  $\sigma_1$  (the beam size in a case where the energy spread is zero) due to the emittance decreases to the minimum value. However, the beam width caused by the energy dispersion becomes larger than the beam width caused by the emittance. In a case where the ion beam in such a state is cut by the slit,

the spatial distribution is cut sharply, but the energy distribution has a cut shape rounded by the energy spread corresponding to  $2\sigma_1$ . In other words, for example, even when the slit width is set to the dimension corresponding to 3% of the energy spread, a part of the ions having an energy difference with respect to the predetermined implantation energy smaller than 3% collide with the wall of the slit so as to disappear, but a part of the ions having an energy difference larger than 3% pass through the slit.

The energy analysis slit is installed at a position where the value of  $\sigma_1$  becomes minimal. Since the value of  $\sigma_1$  decreases to an ignorable value by the slit width at the position, the energy distribution is also cut sharply like the space distribution. For example, even in a case where the opening width of the energy analysis slit is also set to the dimension (0.03  $\eta$ ) corresponding to 3% of the energy spread, all ions having an energy difference exceeding 3% and passing through the energy width confining slit are interrupted at the position. As a result, when the beam having a rectangular energy distribution at first passes through two slits, a dome-shaped distribution is formed in which the energy becomes a peak value at 0%, the height decreases by a half at  $\pm 3\%$ , and the energy abruptly decreases to zero. Since the number of the ions having a small energy difference relatively increases, the energy width substantially decreases compared to the case where only one energy analysis slit is provided and the ion beam passes through the slit while having a substantially rectangular energy distribution.

In the double slit system, when the energy of the beam accelerated by the linac is slightly deviated from the predetermined implantation energy by the effect of cutting the end of the energy distribution, there is an effect that the energy deviation of the passed beam decrease. For example, in a case where the energy deviation is 3% when the energy spread is  $\pm 3\%$ , the positive side of the energy having the dome-shaped distribution in the energy distribution of the ion beam passing through the double slit becomes a half, and hence a difference between an actual energy gravity center and an ideal energy gravity center approximately becomes  $\Delta E/E=1\%$ . Meanwhile, when the ion beam is cut by the single energy analysis slit, the difference between an actual energy gravity center and an ideal energy gravity center approximately becomes  $\Delta E/E=1.5\%$ . The effect of rounding the distribution is essentially exhibited in a direction in which the deviation of the energy center is suppressed.

In this way, in order to improve the energy precision by decreasing both the energy spread and the deviation of the energy center using the acceleration system having both the energy spread and the energy deviation, the limitation of the energy using the double slit is effective.

Since the energy analysis electromagnet needs high magnetic field precision, highly precise measurement devices **86a** and **86b** for precisely measuring the magnetic field are provided (see FIG. 5B). The measurement devices **86a** and **86b** use the MRP to calibrate the hall probe and uses the hall probe to control the constant magnetic field feedback control by the appropriate combination of the nuclear magnetic resonance (NMR) probe called the magnetic resonance probe (MRP) and the hall probe. Further, the energy analysis electromagnet is produced by high precision so that the non-uniformity of the magnetic field becomes smaller than 0.01%. Further, each electromagnet is connected with a power supply having current setting precision and current stability of  $1 \times 10^{-4}$  or more and a control device thereof.

Further, the quadrupole lens **26** as the lateral focusing lens is disposed between the energy analysis slit **28** and the energy analysis electromagnet **24** at the upstream side of the energy

analysis slit **28**. The quadrupole lens **26** may be formed in an electric field type or a magnetic field type. Accordingly, since the energy dispersion is suppressed after the ion beam is deflected in a U-shape and the beam size decreases, the beam may be transported with high efficiency. Further, since the conductance decreases at the magnetic pole portion of the deflection electromagnet, it is effective to dispose a vacuum pump exhausts outgas in the vicinity of, for example, the energy analysis slit **28**. In a case where a magnetically levitated turbo molecular pump is used, the pump needs to be provided at a position where the pump is not influenced by the leakage magnetic field of the electromagnet of the energy analysis electromagnet **24** or the deflection electromagnet **30**. By the vacuum pump, the beam current degradation due to the scattering of the remaining gas at the deflection unit is prevented.

When there is a large installation error in the quadrupole lens in the high energy multistage linear acceleration unit **14**, the dispersion adjusting quadrupole lens **26**, or the beam focusing/defocusing device **32**, the center orbit of the beam illustrated in FIG. 5B is distorted, and the beam may easily disappear while contacting the slit. As a result, the final implantation angle and the final implantation position are also wrong. Here, the center orbit of the beam essentially passes through the center of the beam scanner **34** on the horizontal plane due to the magnetic field correction value of the deflection electromagnet **30** having an implantation angle correction function. Accordingly, the deviation of the implantation angle is corrected. Further, when an appropriate offset voltage is applied to the beam scanner **34**, the distortion of the center orbit from the scanner to the wafer disappears, and hence the horizontal deviation of the implantation position is solved.

The ions that pass through the deflection electromagnets of the beam deflection unit **16** are subjected to a centrifugal force and a Lorentz force, and hence draws a circular-arc orbit by balance of these forces. When this balance is represented by a relation, a relation of  $mv=qBr$  is established. Here,  $m$  indicates the mass of the ion,  $v$  indicates the velocity of the ion,  $q$  indicates the charge state of the ion,  $B$  indicates the magnetic flux density of the deflection electromagnet, and  $r$  indicates the curvature radius of the orbit. Only the ions in which the curvature radius  $r$  of the orbit matches the curvature radius of the magnetic center of the deflection electromagnet may pass through the deflection electromagnet. In other words, in a case where the ions have the same charge state, the ions that may pass through the deflection electromagnet applied with the uniform magnetic field  $B$  are only the ions having the specific momentum  $mv$ . The EFM is called the energy analysis electromagnet, but is actually a device that is used to analyze the momentum of the ion. The BM or the mass analysis electromagnet of the ion generation unit is the momentum filter.

Further, the beam deflection unit **16** may deflect the ion beam by  $180^\circ$  just by using a plurality of magnets. Accordingly, the high energy ion implanter **100** in which the beam-line has a U-shape may be realized by a simple configuration.

As illustrated in FIG. 5A, the beam deflection unit **16** deflects the ion beam emitted from the high energy multistage linear acceleration unit **14** by  $90^\circ$  using the energy analysis electromagnet **24**. Then, the beam path is further deflected by  $90^\circ$  using the deflection electromagnet **30** that is also used to correct the orbit, and is incident to the beam focusing/defocusing device **32** of the beam transportation line unit **18** to be described later. The beam focusing/defocusing device **32** focuses or defocuses the incident beam and supplies the beam to the beam scanner **34**. Further, the defocusing of the beam due to the energy dispersion is prevented by the lens effect of



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the quadrupole lens **26** illustrated in FIG. **5B** or an extreme decrease in the size of the beam is prevented by using the beam expansion effect based on the energy dispersion.

FIG. **11A** is a schematic top view illustrating a quadrupole lens as a lateral focusing lens, and FIG. **11B** is a schematic front view illustrating the quadrupole lens. The top view of FIG. **11A** illustrates the electrode length in the beamline traveling direction of the quadrupole lens **26** and the effect in which the beam that defocuses laterally with respect to the beam of the energy selected by the energy analysis electromagnet (the EFM deflection magnet) **24** focuses laterally by the quadrupole lens **26**. The front view of FIG. **11B** illustrates the lateral focusing effect of the beam based on the focusing/defocusing action of the electrode of the quadrupole lens **26**.

As described above, the beam deflection unit **16** performs the deflection of the ion beam by 180° by a plurality of electromagnets between the high energy multistage linear acceleration unit **14** and the beam transportation line unit **18** in the ion implanter that accelerates the ions generated from the ion source and transports the ions to the wafer so as to implant the ions thereto. That is, the energy analysis electromagnet **24** and the orbit correction deflection electromagnet **30** are respectively formed so as to have deflection angles of 90°. As a result, the total deflection angle becomes 180°. Furthermore, the amount of the deflection performed by one magnet is not limited to 90°, and may be the following combination.

- (1) One magnet having deflection amount of 90°+two magnets having deflection amounts of 45°
- (2) Three magnets having deflection amounts of 60°
- (3) Four magnets having deflection amounts of 45°
- (4) Six magnets having deflection amounts of 30°
- (5) One magnet having deflection amount of 60°+one magnet having deflection amount of 120°
- (6) One magnet having deflection amount of 30°+one magnet having deflection amount of 150°

The beam deflection unit **16** as the energy analysis unit is a folding path in the U-shaped beamline, and the curvature radius *r* of the deflection electromagnet forming the unit is an important parameter that limits the maximum energy of the beam to be transported and determines the entire width of the apparatus or the width of the center maintenance area (see FIGS. **5A** and **5B**). When the value is optimized, an increase in the entire width of the apparatus is suppressed without decreasing the maximum energy. Then, the gap between the high energy multistage linear acceleration unit **14** and the beam transportation line unit **18** is widened, so that a sufficient work space *R1* is ensured (see FIG. **1**).

FIGS. **12A** and **12B** are perspective views illustrating an example of a configuration of the electromagnet. FIG. **13** is a schematic view illustrating an opening and closing portion provided in the electromagnet. For example, as illustrated in FIGS. **12A** and **12B**, the electromagnet forming the energy analysis electromagnet **24** or the deflection electromagnet **30** includes an upper yoke **87**, a lower yoke **88**, inner and outer yokes **89a** and **89b**, an upper pole (not illustrated), a lower pole **93**, an upper coil **91a**, and a lower coil **91b**. Further, as illustrated in FIG. **13**, the outer yoke **89b** is divided into two members **89b1** and **89b2**, and the two members may be opened outward as folding double doors by opening and closing portions **92a** and **92b**. Then, a beam guide container (not illustrated) forming the beamline may be removably attached thereto.

Further, the vacuum container (chamber) of the center portion of the beam deflection unit **16**, for example, the container accommodating the energy width confining slit **27**, the quadrupole lens **26**, the energy analysis slit **28**, and the like may

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be easily attached to and detached from the beamline. Accordingly, it is possible to simply enter and exit the work area of the center of the U-shaped beamline during the maintenance work.

The high energy multistage linear acceleration unit **14** includes a plurality of linear accelerators that accelerate the ions. Each of the plurality of linear accelerators includes a common connection portion, and the connection portion may be removably attached to the energy analysis electromagnet **24** located at the upstream side in relation to the energy analysis slit **28** in the plurality of electromagnets. Similarly, the beam transportation line unit **18** may be removably attached to the deflection electromagnet **30**.

Further, the energy analysis electromagnet **24** that is installed at the upstream side of the energy analysis slit **28** and includes the electromagnet may be formed so as to attached and detached or connected to the upstream high energy multistage linear acceleration unit **14**. Further, in a case where the beam transportation line unit **18** to be described later is configured as a module type beamline unit, the deflection electromagnet **30** that is installed at the downstream side of the energy analysis slit **28** may be attached and detached or connected to the downstream beam transportation line unit **18**.

The linac and the beam deflection unit are respectively disposed on plane trestles, and are formed so that the ion beam orbit passing through the units are substantially included in one horizontal plane (the orbit after the deflection of the final energy filter is excluded).

(Beam Transportation Line Unit)

FIG. **6A** is a top view illustrating a schematic configuration from the beam scanner to the substrate processing/supplying unit along the beamline after the beam collimator, and FIG. **6B** is a side view illustrating a schematic configuration from the beam scanner to the substrate processing/supplying unit along the beamline after the beam collimator.

Only the necessary ion species are separated by the beam deflection unit **16**, and the beam that is formed only by the ions having a necessary energy value is focused or defocused in a desired cross-sectional shape by the beam focusing/defocusing device **32**. As illustrated in FIGS. **5A** to **6B**, the beam focusing/defocusing device **32** is configured as (an electric field type or a magnetic field type) focusing/defocusing lens group such as a Q (quadrupole) lens. The beam having a focused/defocused cross-sectional shape is scanned in a direction parallel to the surface of FIG. **1A** by the beam scanner **34**. For example, the beam focusing/defocusing device is configured as a triplet Q lens group including a lateral focusing (longitudinal defocusing) lens QF/a lateral defocusing (a longitudinal focusing) lens QD/a lateral focusing (a longitudinal defocusing) lens QF. If necessary, the beam focusing/defocusing device **32** may be configured by each of the lateral focusing lens QF and the lateral defocusing lens QD or the combination thereof.

As illustrated in FIGS. **5A** and **5B**, the faraday cup **80b** (called a resolver-faraday cup) for measuring the total beam current of the ion beam is disposed at a position directly before the beam focusing/defocusing device **32** of the foremost portion inside the scanner housing.

FIG. **14A** is a schematic front view illustrating the resolver-faraday cup **80b**, and FIG. **14B** is a schematic view illustrating an operation of the resolver-faraday cup **80b**.

The resolver-faraday cup **80b** is formed so as to be extracted in the vertical direction on the beamline by a driving mechanism, and is formed so that the opening faces the upstream side of the beamline while having a rectangular square shape in the horizontal direction. The resolver-faraday

cup is used to completely interrupt the ion beam that reaches the downstream side of the beamline if necessary other than the purpose of measuring the total beam current of the ion beam during the adjustment of the linac and the beam deflection portion. Further, the resolver-faraday cup **80b**, the beam scanner **34**, a suppression electrode **74**, and ground electrodes **76a**, **78a**, and **78b** are accommodated in a scanner housing **82**.

The beam scanner **34** is a deflection scan device (called a beam scanner) that causes the ion beam to periodically scan the horizontal direction perpendicular to the ion beam traveling direction in a reciprocating manner by the periodically changing electric field.

The beam scanner **34** includes a pair of (two) counter scan electrodes (bipolar deflection scan electrodes) that are disposed so as to face each other with the ion beam passage region interposed therebetween in the beam traveling direction. Then, a scan voltage that changes to positive and negative values at a predetermined frequency in the range of 0.5 Hz to 4000 Hz and is approximated to the triangular wave is applied to two counter electrodes positive and negative inversely. The scan voltage generates a changing electric field that deflects the beam passing through the gap between two counter electrodes. Then, the beam that passes through the gap is scanned in the horizontal direction by the periodic change of the scan voltage.

The amount of the crystal damage generated inside the silicon wafer during the high energy ion implantation is inverse proportional to the scan frequency. Then, there is a case in which the amount of the crystal damage influences the quality of the produced semiconductor device. In such a case, the quality of the produced semiconductor device may be improved by freely setting the scan frequency.

Further, an offset voltage (a fixed voltage) is superimposed on the scan voltage in order to correct the amount of the beam positional deviation measured directly near the wafer in a state where the scan voltage is not applied thereto. Accordingly, the scan range is not deviated in the horizontal direction due to the offset voltage, and hence the bilaterally symmetrical ion implantation may be performed.

The suppression electrode **74** that includes an opening in the ion beam passage region is disposed between two ground electrodes **78a** and **78b** at the downstream side of the beam scanner **34**. The ground electrode **76a** is disposed before the scan electrode at the upstream side thereof, but if necessary, the suppression electrode having the same configuration as that of the downstream side may be disposed. The suppression electrode suppresses the intrusion of electrons to the positive electrode.

Further, a ground shielding plate **89** is disposed at each of the upper and lower sides of deflection electrodes **87a** and **87b**. The ground shielding plate prevents the secondary electrons accompanied by the beam from flowing to the positive electrode of the beam scanner **34** from the outside. The power supply of the scanner is protected by the suppression electrode and the ground shielding plate, and hence the orbit of the ion beam is stabilized.

A beam parking function is provided at the rear side of the beam scanner **34**. The beam parking function is formed so that the ion beam passing through the beam scanner is largely deflected in the horizontal direction if necessary so as to be led to the beam dump.

The beam parking function is a system that instantly stops the transportation of the beam within 10  $\mu$ s in a case where an implantation error such as a dose uniformity error occurs when an unexpected problem such as a discharge of an electrode occurs during the ion implantation and an implantation operation is continued. In fact, at the moment in which the

noticeable degradation in the beam current is detected, the output voltage of the beam scanner power supply is increased to 1.5 times the voltage corresponding to the maximum scan width, and the beam is led to the beam dump near the parallelizing lens. The beam irradiation position on the wafer at the moment in which the problem occurs is stored, and the beam is returned to the original orbit at the moment in which the wafer moves for the scanning operation in the vertical direction moves to the position after the problem is solved, thereby continuing the ion implantation as if no problem occurs.

In this way, the power supply having high responsiveness may not supply a high voltage (due to the main problem in cost). Meanwhile, in order to obtain the uniformity of the high-degree implantation dose, the scan range needs to be wider than the wafer. For this reason, the beam scanner needs to have an ability of sufficiently deflecting the high energy beam. This may be realized when the gap and the length of the deflection electrode of the beam scanner are limited. In the energy region of the invention, the electrode length may be five times or more the gap.

A beam drift space portion is provided in a long section at the downstream side of the beam scanner **34** inside the scan housing, and hence a sufficient scan width may be obtained even when the beam scan angle is narrow. At the rear side of the scan housing located at the downstream side of the beam drift space portion, the deflected ion beam is adjusted to be directed to the direction of the ion beam before the beam is deflected. That is, the beam collimator **36** is installed which curves the beam so as to be parallel to the beamline.

Since the aberration (a difference in focal distance between the center portion of the beam collimator and left and right ends) generated in the beam collimator **36** is proportional to the square of the deflection angle of the beam scanner **34**, the aberration of the beam collimator may be largely suppressed when the beam drift space portion is increased in length and the deflection angle is decreased. If the aberration is large, the center portion and the left and right ends have different beam sizes and beam divergence angles when the ion beam is implanted into the semiconductor wafer, and hence the quality of the product becomes non-uniform.

Further, when the length of the beam drift space portion is adjusted, the length of the beam transportation line unit may match the length of the high energy multistage linear acceleration unit **14**.

FIG. 7 is a schematic top view illustrating a main part of an example of the beam scanner. FIG. 8 is a schematic side view illustrating a main part of an example of the beam scanner. FIG. 9 is a schematic front view illustrating a structure in which an example of the beam scanner is removably attached to the halfway position of the ion beamline when viewed from the downstream side.

As illustrated in FIGS. 7 and 8, in a beam scanner **134**, a pair of deflection electrodes **128** and **130** and ground electrodes **132** and **133** assembled near the upstream and downstream sides thereof are accommodated and installed inside a box **150**. An upstream opening (not illustrated) and an opening **152A** larger than the opening of the ground electrode **133** are respectively provided at the positions corresponding to the openings of the ground electrodes **132** and **133** at the upstream side surface and the downstream side surface of the box **150**.

The connection between the deflection electrode and the power supply is realized in the feed through structure. Meanwhile, the upper surface of the box **150** is provided with a terminal and a ground terminal used to connect the deflection electrodes **128** and **130** to the power supply. Further, a handle which is suitable for the attachment or the transportation is

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provided at each of side surfaces of the box **150** parallel to the beam axis. Furthermore, the box **150** is provided with a vacuum exhaust opening that decreases the pressure inside the beam scanner **134**, and the vacuum exhaust opening is connected to a vacuum pump (not illustrated).

As illustrated in FIG. 9, the box **150** is slidably provided in a beam guide box **170** fixed onto a trestle **160**. The beam guide box **170** is sufficiently larger than the box **150**, and the bottom portion thereof is provided with two guide rails for sliding the box **150**. The guide rail extends in a direction perpendicular to the beam axis, and the side surface of the beam guide box **170** of one end side thereof may be opened and closed by a door **172**. Accordingly, the box **150** may be simply extracted from the beam guide box **170** during the repair and the check of the beam scanner **134**. Furthermore, in order to lock the box **150** press-inserted into the beam guide box **170**, the other end of the guide rail is provided with a locking mechanism (not illustrated).

The scanner peripheral unit members are work targets during the maintenance of the beamline, and the maintenance work may be easily performed from the work space R1. Similarly, the maintenance work of the high energy multistage linear acceleration unit **14** may be easily performed from the work space R1.

The beam collimator **36** is provided with an electric field collimating lens **84**. As illustrated in FIGS. 6A and 6B, the electric field collimating lens **84** includes a plurality of acceleration electrode sets and a plurality of deceleration electrode sets substantially having a hyperbolic shape. Each of the pair of electrodes faces each other with an acceleration-deceleration gap interposed therebetween and having a width not causing a discharge, and the acceleration-deceleration gap forms an electric field that is strengthened in proportional to a distance between the reference axis and the axial element causing the acceleration or deceleration of the ion beam and having an element of influencing the lateral focusing of the ion beam.

The downstream electrode in the pair of electrodes with the acceleration gap interposed therebetween and the upstream electrode of the deceleration gap are formed as an integrated structure and the downstream electrode of the deceleration gap and the upstream electrode of the next acceleration gap are formed as an integrated structure so as to have the same potential. As illustrated in FIG. 6B, each of the structures includes an upper unit and a lower unit, and a space portion through which the ion beam passes is formed between the upper unit and the lower unit.

From the upstream side of the electric field collimating lens **84**, the first electrode (the incident electrode) and the final electrode (the emission electrode) are maintained at the ground potential. Accordingly, the energy of the beam at the positions before and behind the collimating lens **84** does not change.

In the intermediate electrode structure, the exit electrode of the acceleration gap and the entrance electrode of the deceleration gap are connected with a negative power supply **90** having a variable constant voltage, and the exit electrode of the deceleration gap and the entrance electrode of the acceleration gap are connected with a positive power supply having a variable constant voltage (at the n-stage, negative, positive, negative, positive, negative, and the like). Accordingly, the ion beam is gradually directed toward a direction parallel to the trajectory center of the beamline while being accelerated and decelerated repeatedly. Finally, the ion beam reaches the orbit parallel to the ion beam traveling direction (the beamline orbit direction) before the deflection scanning operation.

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In this way, the beam that is scanned by the beam scanner **34** becomes parallel to the axis (the reference axis) of the deflection angle  $0^\circ$  parallel to the ion beam traveling direction (the beamline orbit direction) before the scan operation by the beam collimator **36** including the electric field collimating lens and the like. At this time, the scan region is formed so as to be bilaterally symmetrical to each other with respect to the reference axis.

The ion beam that is emitted from the electric field collimating lens **84** is sent to the electric field final energy filter **38** (AEF (**94**): Angular Energy Filter). In the final energy filter **94**, a final analysis is performed on the energy of the ion beam to be directly implanted into the wafer, only the ion species having a necessary energy value are selected, and the neutralized particles or the ions having a different ion charge state are removed. The final energy filter **94** of the electric field deflection is configured as a plate-shaped deflection electrode including a pair of plane or curved surfaces facing each other in the vertical direction of the beamline orbit direction, is curved downward by the deflection action of the final energy filter **94** in the vertical direction of the beamline orbit direction, and is curved so as to match the ion beam orbit.

As illustrated in FIGS. 6A and 6B, the electric field deflection electrode is configured as a pair of AEF electrodes **104**, and is disposed so that the ion beam is interposed from the vertical direction. In the pair of AEF electrodes **104**, a positive voltage is applied to the upper AEF electrode **104**, and a negative voltage is applied to the lower AEF electrode **104**. During the deflection by the electric field, the ion beam is deflected downward by about  $10$  to  $20^\circ$  by the action of the electric field generated between the pair of AEF electrodes **104**, and hence only the ion beam having target energy is selected. As illustrated in FIG. 6B, only the ion beam having a charge state selected in the final energy filter **94** is deflected downward at the set orbit angle. The beam that is formed by only the ions selected in this way is uniformly irradiated to the wafer **200** as the irradiation target at an accurate angle.

In a case where the high energy beam is actually deflected, a pair of plate-shaped deflection electrodes **204** facing each other in the vertical direction is divided into n number of segments in the longitudinal direction in accordance with the deflection angle and the curvature radius when the deflection electrodes are curved so as to match the ion beam orbit as illustrated in FIG. 10. Thus, the production precision or the economic efficiency is excellent in the plate-shaped electrode of which the upper electrode and the lower electrode are maintained at the same potential. Further, the plate-shaped deflection electrode that is divided into n number of segments in the longitudinal direction may be formed as n number of upper and lower plate-shaped electrodes set to different potentials other than the configuration in which the upper electrode and the lower electrode are maintained at the same potential.

With such a structure, the electric field type energy filter may be mounted on the high energy scan beam transportation line. Since the beam is deflected in a direction perpendicular to the beam scan surface by the electric field, the energy analysis may be performed without influencing the implantation ion density distribution (the uniformity) in the beam scan direction.

Further, in addition to the mounted final energy filter, the beamline is equipped with three kinds of beam filters, that is, the radio frequency linear accelerator of the high energy multistage linear acceleration unit **14**, the magnetic field type EFM (the energy analysis electromagnet **24**) and the BM (the deflection electromagnet **30**) of the U-shaped deflection portion, and the final energy filter. As described above, the radio

frequency linear accelerator is the velocity (v) filter, the EFM and the BM are the momentum (mv) filters, and the final energy filter is the energy ( $mv^2/2$ ) filter as its name. In this way, when the different triple filters are used, a very pure ion beam that has high energy purity compared to the related art and has a small amount of particles or metal contamination may be supplied to the wafer.

Furthermore, in function, the EFM removes the energy contamination sneaking through the radio frequency linear accelerator or limits the energy width with high resolution, and the AEF mainly removes the ions subjected to a change in charge state by the resist outgas by the beam transportation line unit after the energy analysis using the EFM with comparatively low resolution.

The final energy filter **94** includes a ground electrode **108** that is provided at the upstream side of the final energy filter **94** and an electrode set provided with an AEF suppression electrode **110** provided between two ground electrodes at the downstream side. The AEF suppression electrode **110** suppresses the intrusion of the electrons to the positive electrode.

Dose cups **122** that are disposed at the left and right ends of the most downstream ground electrode of the final energy filter **94** measure the amount of the beam current to be implanted based on the dose amount.

(Substrate Processing/Supplying Unit)

In FIG. 6A, the arrow near the wafer **200** indicates the beam scanned in the arrow direction. Then, in FIG. 6B, the arrow near the wafer **200** indicates the reciprocation movement, that is, the mechanical scanning operation of the wafer **200** in the arrow direction. That is, when the beam is scanned in a reciprocating manner in, for example, one axial direction, the wafer **200** is driven by a driving mechanism (not illustrated) so that the wafer moves in a reciprocating manner in a direction perpendicular to the one axial direction.

The substrate processing/supplying unit **20** that supplies the wafer **200** to a predetermined position and performs an ion implantation thereon is accommodated in a process chamber (an implantation process chamber) **116**. The process chamber **116** communicates with an AEF chamber **102**. An energy defining slit (EDS) **118** is disposed inside the process chamber **116**. The energy defining slit **118** is formed as a slit that is laterally long in the scan direction in order to separate only the ion beam having a meaningful energy value and a meaningful charge state and passing through the AEF by limiting the passage of the ion beam having a non-meaningful energy value and a non-meaningful charge state. Further, the energy defining slit **118** forms a slit body by a movable member in the vertical direction so as to adjust the separation gap of the slit, and may be used for various measurement purposes such as an energy analysis or an implantation angle measurement. Further, the movable upper and lower change slit members include a plurality of slit surfaces, and the slit width may be changed to a desired slit width in a manner such that the slit surfaces are changed and the axes of the upper and lower slits are adjusted or rotated in the vertical direction. A configuration may be also employed which decreases the cross contamination by sequentially changing the plurality of slit surfaces in response to the ion type.

A plasma shower **120** supplies low-energy electrons to the entire surface of the wafer **200** and the ion beam on the orbit in response to the beam current amount of the ion beam, and suppresses the charge-up of the positive charge generated in the ion implantation. Furthermore, a dose cup (not illustrated) that measures the dose amount may be disposed at each of left and right ends of the plasma shower **120** instead of the dose cups **122** disposed at the left and right ends of the most downstream ground electrode of the final energy filter **94**.

A beam profiler **124** includes a beam profiler cup (not illustrated) that measures the beam current at the ion implantation position. The beam profiler **124** measures the ion beam density at the ion implantation position in the beam scan range while moving in the horizontal direction before the ion implantation. In a case where the predicted non-uniformity (PNU) of the ion beam does not satisfy the request of the process as a result of the beam profile measurement, the PNU is automatically adjusted to satisfy the process condition by correcting the control function of the application voltage of the beam scanner **34**. Further, a configuration may be also employed in which a vertical profile cup (not illustrated) is provided in parallel to the beam profiler **124**, the beam shape and the beam X-Y position are measured, the beam shape at the implantation position is checked, and the implantation angle or the beam divergence angle is checked by the combination of the beam width, the beam center position, and the divergence mask.

A lateral elongated faraday cup **126** with a beam current measurement function capable of measuring the ion beam in the scan range in the wafer region is disposed at the most downstream side of the beamline, and is configured to measure the final setup beam. FIG. 15 is a schematic front view illustrating the lateral elongated faraday cup. Furthermore, in order to reduce the cross contamination, the lateral elongated faraday cup **126** may include a changeable bottom surface of a faraday cup of a tripe surface structure capable of changing three surfaces of a triangular prism in response to the ion type. Further, a configuration may be also employed in which a vertical profile cup (not illustrated) is provided in parallel to the lateral elongated faraday cup **126**, the beam shape or the vertical beam position is measured, and the implantation angle or the beam divergence angle in the vertical direction at the implantation position is monitored.

As described above, the high energy ion implanter **100** is formed so that the units are disposed in a U-shape so as to surround the work space R1 as illustrated in FIG. 1. For this reason, a worker in the work space R1 may perform the replacement, the maintenance, and the adjustment of the parts of many units.

(Consideration of Entire Layout, Maintenance Workability, Manufacturability, and Global Environment)

The high energy ion implanter **100** according to the embodiment accelerates the ion beam generated in the ion beam generation unit **12** by the high energy multistage linear acceleration unit **14**, changes the direction of the ion beam by the beam deflection unit **16**, and irradiates the ion beam to the substrate existing in the substrate processing/supplying unit **20** provided at the termination end of the beam transportation line unit **18**.

Further, the high energy ion implanter **100** includes the high energy multistage linear acceleration unit **14** and the beam transportation line unit **18** as the plurality of units. Then, the high energy multistage linear acceleration unit **14** and the beam transportation line unit **18** are disposed so as to face each other with the work space R1 illustrated in FIG. 1 interposed therebetween. Accordingly, since the high energy multistage linear acceleration unit **14** and the beam transportation line unit **18** disposed substantially linearly in the apparatus of the related art are disposed in a folded state, an increase in the entire length of the high energy ion implanter **100** may be suppressed. Further, the curvature radiuses of the plurality of deflection electromagnets forming the beam deflection unit **16** are optimized so as to minimize the width of the apparatus. With such a configuration, the installation area of the apparatus is minimized, and the maintenance or the like of the high energy multistage linear acceleration unit **14** or the

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beam transportation line unit **18** may be performed in the work space R1 interposed between the high energy multistage linear acceleration unit **14** and the beam transportation line unit **18**.

Further, the plurality of units constituting the high energy ion implanter **100** includes the ion beam generation unit **12** that is provided at the upstream side of the beamline and generates the ion beam, the substrate processing/supplying unit **20** that is provided at the downstream side of the beamline and supplies the substrate so as to perform a process in which ions are implanted into the substrate, and the beam deflection unit **16** that is provided at the halfway position of the beamline from the ion beam generation unit **12** toward the substrate processing/supplying unit **20** and deflects the orbit of the ion beam. Then, the ion beam generation unit **12** and the substrate processing/supplying unit **20** are disposed at one side of the entire beamline, and the beam deflection unit **16** is disposed at the other side of the entire beamline. Accordingly, since the ion source **10** that needs to be subjected to the maintenance within a comparatively short time and the substrate processing/supplying unit **20** that needs to supply and acquire the substrate are disposed so as to be adjacent to each other, the movement area of the worker may be small.

Further, the high energy multistage linear acceleration unit **14** includes a plurality of linear accelerators that accelerate the ions, and each of the plurality of linear accelerators may include a common connection portion. Accordingly, the number or the type of the linear accelerator may be easily changed in response to the energy necessary for the ions implanted into the substrate.

Further, the beam scanner **34** as the scanner device and the beam collimator **36** as the collimating lens device may include a standard-shaped connection portion with respect to the adjacent units. Accordingly, the number or the type of the linear accelerator may be easily changed. Then, the beam scanner **34** or the beam collimator **36** may be selected in response to the configuration and the number of the linear accelerator included in the high energy multistage linear acceleration unit **14**.

Further, in the high energy ion implanter **100**, the alignment (the positional adjustment) of the beam may be performed by integrating the vacuum chamber and the frame of each device and performing the assembly in accordance with the reference position of the vacuum chamber or the frame of the device. Accordingly, the troublesome alignment operation may be minimized, and the device set-up time may be shortened. Accordingly, the deviation of the axis caused by the mistake in work may be suppressed. Further, the alignment of the vacuum chambers may be performed by the unit of the module. Accordingly, the work load may be reduced. Further, the size of the modulated device may be decreased to be equal to or smaller than the size in which the device may easily move. Accordingly, the relocation load of the module or the high energy ion implanter **100** may be reduced.

Further, the high energy ion implanter **100** may be formed so that the high energy multistage linear acceleration unit **14**, the beam transportation line unit **18**, the exhaust device, and the like are assembled to a single trestle. Further, the high energy ion implanter **100** is formed so that the high energy multistage linear acceleration unit **14**, the beam deflection unit **16**, and the beam transportation line unit **18** are included in one plane on the plane base. Accordingly, since each block of the high energy ion implanter **100** may be directly transported while the blocks are fixed onto one plane base, a deviation in adjustment hardly occurs, and hence an effort for re-adjusting the blocks on site may be reduced. For this rea-

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son, it is possible to prevent an uneconomical problem in which many experts are sent to the installation site for a long period of time.

Further, when the plane base is formed in the middle portion of the trestle instead of the floor thereof, only the devices directly involved with the ion beam orbit may be mounted onto the plane base. Then, when a component such as a radio frequency cubic circuit as an auxiliary device may be assembled in the space formed below the plane base, the space utilization efficiency may be improved, and hence the ion implanter having a compacter size may be realized.

Thus, the high energy ion implanter **100** may be also installed in a site where a sufficient installation place is not ensured, and may be used in a manner such that the high energy ion implanter is transported to a demanded place in a state where the apparatus is assembled and adjusted inside a production factory, is fixed at the installation site, and is used by the final adjustment. Further, the high energy ion implanter **100** may realize the high energy ion implantation while satisfying the standard level of the semiconductor production line of the semiconductor production factory.

In this way, the high energy ion implanter **100** may be decreased in size compared to the related art by examining the layout of the units or the devices, and hence may have an installation length that is about a half of the size of the related art. Further, the ion implanter according to the embodiment may be operated in a manner such that the components are assembled to the bases inside the production factory, are loaded in a transportation vehicle to be transported to the installation site while the ion beam orbit is established through the positional adjustment on the bases, are fixed to the trestles, and then the deviation in adjustment is finely adjusted to be removed. For this reason, the ion implanter may be remarkably easily and reliably adjusted on site by a person who is not an expert, and hence the set-up time may be shortened.

Further, when the layout like the elongated U-shaped folded beamline is employed, the ion implanter capable of highly precisely implanting the high energy ions of 5 to 8 MeV in maximum may be realized. Further, the ion implanter includes a small installation area and a sufficient maintenance area by the layout having a center passage (a center region). Further, the power consumption may be decreased by the low-power consumption operation using the electric field parallel lens, the electric field type scanner, the electric field AEF, and the like during the operation of the ion implanter. In other words, the ion implanter according to the embodiment may perform the low-power consumption operation by employing the scan beam parallelization mechanism using the electric field deflection type collimating lens device.

While the invention has been described by referring to the above-described embodiment, the invention is not limited to the above-described embodiment, and the appropriate combination of the configurations of the embodiment or the substitution thereof is also included in the invention. Further, the combination of the embodiments or the process sequence thereof may be appropriately set or various modifications in design may be added to the embodiments based on the knowledge of the person skilled in the art. An embodiment having such modifications may be also included in the scope of the invention.

Hereinafter, another aspect of the invention will be described according to embodiments.

In the above-described high energy ion implanter, each device included in at least the beam transportation unit is of

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the electric field type, and hence the configuration of the device may be simplified or the power supply may have a low output.

FIG. 16A is a top view illustrating a schematic configuration from the beam focusing/defocusing device 32 to the beam scanner 34 according to the embodiment, and FIG. 16B is a side view illustrating a schematic configuration from the beam focusing/defocusing device 32 to the beam scanner 34 according to the embodiment.

As illustrated in FIGS. 16A and 16B, the electric field type beam scanner 34 includes a pair of deflection electrodes 87a and 87b. Further, a ground shielding plate 89 is disposed above and below the deflection electrodes 87a and 87b. The ground shielding plate 89 prevents the secondary electrons accompanied by the beam from flowing to the electrode of the beam scanner 34 from the outside. When the gap between the parallel portions of the pair of deflection electrodes 87a and 87b from the outside is indicated by  $W_1$  and the length of each of the deflection electrodes 87a and 87b in the beam traveling direction is indicated by  $L_1$ , a relation of  $L_1 \geq 5W_1$  may be satisfied. Further, the power supply (the amplifier) may be operated at an arbitrary scan frequency of 0.5 Hz to 4 kHz. Further, when the gap between the pair of deflection electrodes 87a and 87b without parallel portions is indicated by  $D_1$ , a relation of  $L_1 \geq 5D_1$  may be satisfied.

Generally, in order to sufficiently deflect the high energy beam, the beam needs to pass through a high electric field by a long distance. In order to form the high electric field, there is a need to use high voltage or narrow the electrode gap. Further, the beam scanner needs to use a high-voltage power supply capable of changing the voltage at the frequency of about 1 kHz, but it is generally difficult to output a high voltage in this kind of power supply. Thus, there is a need to narrow the gap between the deflection electrodes in the beam scanner.

The gap between the deflection electrodes 87a and 87b needs to be larger than the width of the passing beam. Accordingly, the minimum gap of the electrode is determined. Further, the length of the electrode is determined by the beam energy, the electric field, and the deflection angle. Further, the beam energy is determined by the specification of the device. The electric field is determined by the above-described condition. Thus, the length of the electrode is determined by the determination of the deflection angle.

For example, in the beam scanner according to the embodiment, the gap between the left and right scanner electrodes is set to about 60 mm (the withstanding voltage between the electrodes does not cause any problem on the assumption that the maximum beam size is 40 mm), and the width of the scanner electrode in the beam traveling direction is set to about 460 mm. Further, the scan voltage is  $\pm 30$  kV and the scan frequency is about 0.5 Hz to 4 kHz.

When the gap between the parallel portions of the pair of deflection electrodes 87a and 87b in the electric field type beam scanner 34 is indicated by  $W_1$  and the height of the deflection electrode is indicated by  $H_1$ , a relation of  $H_1 \geq 1.5W_1$  may be satisfied. For the uniform scan of the beam in the entire region, the electric field in the scanner needs to be uniform in the vertical direction. Therefore, when the deflection electrode having a sufficiently high electrode height is used, the electric field may be made uniform.

The deflection electrode 87a (87b) has a rectangular long plate shape, and a surface thereof facing the other deflection electrode 87b (87a) is formed as a plane or a curved surface. Then, the outer surface opposite to the facing surface may have a step shape.

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Further, the facing surface of the deflection electrode 87a (87b) with respect to the other deflection electrode 87b (87a) is formed as a double-stage plane, and the outer surface opposite to the facing surface may have a step shape. Accordingly, the processability (the manufacturability) is improved. In this way, since the outer surface has a simple plane structure, the processing cost may be reduced. Further, when the outer surface has a step shape and is further subjected to the grinding, the weight of the component decreases, and hence the burden of the worker during the attachment work may be reduced.

Further, the surface of the deflection electrode 87b (87a) facing the other deflection electrode 87b (87a) may be formed as a step processed in a saw edge shape. Accordingly, the metal contamination may be suppressed.

Furthermore, as described above, it is desirable that the gap between the deflection electrodes of the beam scanner be narrow. However, since the scanned beam has a width, the beam collides with the electrode when the electrode gap is too narrow. Therefore, the upstream shape of the pair of deflection electrodes is formed in a straight structure in which the deflection electrodes are parallel to each other so that the upstream gap having a non-widened scan width is narrowed, and the pair of deflection electrodes is formed in a shape which is widened by about  $\pm 5^\circ$  toward the downstream side in which the scan width is widened. The widened portion may have a curved shape or a step shape, but the straight structure may be more simply made at low cost.

The high energy ion implanter 100 includes an upstream ground electrode 78a and a downstream ground electrode 78b which are disposed at the downstream side of the beamline of the electric field type beam scanner 34 and each of which has an opening in the ion beam passage region and a suppression electrode 74 which is disposed between the upstream ground electrode 78a and the downstream ground electrode 78b.

FIG. 17 is a schematic view illustrating a relation in size among the opening width of the downstream ground electrode, the opening width of the suppression electrode, and the opening width of the upstream ground electrode. When the width of an opening 78a1 of the upstream ground electrode 78a is indicated by  $W_1$ , the width of an opening 74a1 of the suppression electrode 74 is indicated by  $W_2$ , and the width of an opening 78b1 of the downstream ground electrode 78b is indicated by  $W_3$ , the electrodes may be formed so as to satisfy a relation of  $W_1 \leq W_2 \leq W_3$ . Since the scanned beam is widened in the lateral direction as it goes toward the downstream side, the scanned beam may not collide with the members when the opening widths of the suppression electrode 74 and the ground electrodes 78a and 78b are formed so as to satisfy the above-described relation.

As illustrated in FIG. 16A, the electric field type beam scanner 34 may have a deflection angle of  $\pm 5^\circ$  or less. Accordingly, the incident angle with respect to the downstream electric field type beam collimator 36 (see FIGS. 6A and 6B) decreases, and hence the occurrence of the aberration is suppressed. The aberration (the focal distance difference between the center and the end of the beam collimator) increases in proportional to the incident angle squared.

A beam drift space 96 that decreases the deflection angle of the electric field type beam scanner 34 is provided between the electric field type beam scanner 34 and the electric field type beam collimator 36. Accordingly, the gap between the electric field type beam scanner 34 and the electric field type beam collimator 36 may be widened. For this reason, even when the deflection angle of the electric field type beam scanner 34 is small, the scanned beam is sufficiently widened until the beam reaches the electric field type beam collimator

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A vacuum container 91 that accommodates the electric field type beam scanner 34 and is provided with the beam drift space 96 and a vacuum pump (not illustrated) that is connected to the vacuum container 91 and exhausts a gas inside the vacuum container may be provided. For example, a turbo molecular pump for ensuring the vacuum degree may be provided at the position of the electric field type beam scanner, and a turbo pump may be disposed directly below the electric field type beam scanner. Accordingly, the beamline vacuum degree of the electric field type beam scanner 34 may be ensured. Further, the outgas that is generated by the collision of the ions with respect to the electrode or the aperture near the electric field type beam scanner 34 may be efficiently exhausted. In this way, when the generated gas may be removed as much as possible in the vicinity of the gas generation source, the amount of the gas that is dispersed in the vicinity thereof may be decreased. Further, if there is no unnecessary gas, the beam may pass without the interference of the gas, and hence the beam transportation efficiency is improved.

The electric field type beam collimator 36 (see FIGS. 6A and 6B) is formed so that a focal point F is located in an area between the pair of deflection electrodes 87a and 87b included in the electric field type beam scanner 34 disposed at the upstream side by interposing the beam drift space 96. When the scan range is uniform, the aberration of the beam collimator is inverse proportional to the square of the focal distance. For this reason, the aberration may be suppressed by the installation of the beam collimator 36 having a long focal distance.

FIG. 18 is a schematic view illustrating another example of the beam collimator. An electric field type multistage beam collimator 136 illustrated in FIG. 18 includes multistage collimating lenses 84a, 84b, and 84c. Accordingly, since the scanned beam may be gradually collimated, the gap between the electric field type beam scanner 34 and the electric field type beam collimator 136, for example, the length of the beam drift space 96 may be shortened. For this reason, the entire length of the beamline may be shortened.

As illustrated in FIG. 1, the high energy ion implanter 100 according to the embodiment forms a high energy ion implantation beamline by a first section that includes the high energy multistage linear acceleration unit 14 and the ion beam generation unit 12 with the ion source 10 and includes the elongated trajectory, a second section that changes the direction of the beam by the deflection portion including the beam deflection unit 16, and a third section that includes the beam transportation line unit 18 and the elongated trajectory, and the first section and the third section are disposed so as to face each other, thereby forming the layout of the U-shaped apparatus having facing long line portions.

Further, as illustrated in FIGS. 5A and 5B, the high energy ion implanter 100 has a configuration in which an injector faraday cup 80a that measures the total beam current of the ion beam is provided between the ion beam generation unit 12 and the high energy multistage linear acceleration unit 14 so as to be inserted into and extracted from the beamline.

Similarly, a resolver-faraday cup 80b that measures the total beam current of the ion beam is provided between the beam deflection unit 16 and the beam transportation line unit 18 so as to be inserted into and extracted from the beamline.

Further, as illustrated in FIG. 1, the high energy ion implanter 100 further includes a substrate processing/supplying unit 20 that is disposed at the downstream side of the beam

transportation line unit 18 and performs the ion implantation process. As illustrated in FIGS. 6A and 6B, a fixed lateral elongated faraday cup 126 that measures the total beam current of the ion beam is provided behind the ion implantation position of the substrate processing/supplying unit 20.

Further, as illustrated in FIG. 1 and the like, the high energy ion implanter 100 is configured to generate a beam having a uniform beam focusing/defocusing amount, a small trajectory deviation, and uniform directivity by adjusting the extraction electrode device (the extraction electrode 40: see FIGS. 2A and 2B) that includes the beam direction adjustment portion provided in the ion beam generation unit 12, the adjustment portion (the lateral focusing lens 64a and the longitudinal focusing lens 64b: see FIGS. 5A and 5B) that is provided inside the termination end of the high energy multistage linear acceleration unit 14 and adjusting the beam directivity and the focusing/defocusing degree, the electric field type high energy beam adjustment portion (the orbit adjusting quadrupole lens 26: see FIGS. 5A and 5B) provided in the energy analysis unit (the beam deflection unit 16: see FIG. 1), and the electric field type beam focusing/defocusing device 32 and the electric field type beam collimator 36 that are provided in the beam transportation line unit 18, and to supply the beam to the electric field type beam scanner 34.

As illustrated in FIGS. 16A and 16B, the electric field type beam scanner 34 may be configured to temporarily dump the beam in a manner such that the ion beam is deflected toward the further outside of the normal scan range and is led to any one of the left and right beam dump portions 95a and 95b disposed at the front side of the electric field type beam collimator 36.

Further, the electric field type beam scanner 34 is configured to apply an offset voltage (a constant voltage for causing a position where the electric field becomes zero to deviate from the horizontal center) for correcting the horizontal deflection of the scan range. Further, the beam scanner 34 constitutes a part of a system that finely adjusts the implantation angle and the implantation position by determining the offset voltage based on the back calculation obtained from the beam positional deviation when the beam adjusted to pass through the vicinity of the center of the electric field type beam scanner 34 reaches the wafer.

In the above-described embodiment, the electric field type beam collimator has been described as an example, but a magnetic field type beam collimator may be employed if necessary.

FIG. 19 is a schematic view illustrating a beam current adjuster 300 according to an embodiment of the invention. Although it will be specifically described below, the beam current adjuster 300 includes a variable aperture 302 (or a variable aperture device 302) and a control device 304.

The beam current adjuster 300 is provided in the high energy ion implanter 100 having the high energy multistage linear acceleration unit 14. The beam current adjuster 300 is disposed between the ion beam generation unit 12 and the high energy multistage linear acceleration unit 14. The high energy multistage linear acceleration unit 14 may have a similar configuration to the configuration which is described with reference to FIGS. 1 and 3 and the like. The ion beam generation unit 12 may have a similar configuration to the configuration which is described with reference to FIGS. 1 and 2A and the like. Further, as described above, the high energy ion implanter 100 may include the beam deflection unit 16 that redirects the high energy ion beam accelerated by the high energy multistage linear acceleration unit 14 toward a substrate.

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In FIG. 19, the center orbit of the ion beam is indicated by the reference numeral L similarly to FIG. 5A. The center orbit L is depicted by the one-dotted chain line. Hereinafter, for the convenience of description, the direction along the center orbit L in the high energy multistage linear acceleration unit 14 may be referred to as the Z direction. Then, the Z direction may be called the ion beam transportation direction. In the Z direction, the side which is close to the ion source 10 may be referred to as the upstream side, and the side which is away from the ion source 10 may be referred to as the downstream side. In the embodiment, the Z direction is located within the horizontal plane. In the horizontal plane, a direction which is perpendicular to the Z direction may be referred to as the Y direction, and a direction which is perpendicular to the Z direction and the Y direction may be referred to as the X direction. Further, the X direction may be referred to as the horizontal direction, and the Y direction may be referred to as the vertical direction.

The entrance of the high energy multistage linear acceleration unit 14 is provided with a beam current detector, for example, an injector faraday cup 80a, which may be disposed at the downstream side of the variable aperture 302 to measure a beam current. The beam current detector may enter or exit the center orbit L, and is configured to receive the entirety (that is, the entire XY cross-section of the beam) of the ion beam when the beam current detector is disposed at the center orbit L for the measurement. Thus, the beam current detector is configured to measure the total amount of the beam current.

Further, an entrance Q-lens 174 is provided at the downstream side of the injector faraday cup 80a in the entrance of the high energy multistage linear acceleration unit 14. The entrance Q-lens 174 may be a beamline component which is disposed at the most upstream side of the high energy multistage linear acceleration unit 14. Here, the beamline component means a component of the high energy ion implanter 100 which applies an electric and/or magnetic action to the ion beam to perform, for example, operations including a deflecting operation, an accelerating operation, a decelerating operation, a focusing/defocusing operation, a scanning operation, and the like. The radio frequency resonator 14a (see FIG. 3) is provided at the downstream side of the entrance Q-lens 174.

The ion beam generation unit 12 includes at least one beamline component, for example, the mass analyzer 22. As shown, the bending orbit of the mass analysis magnet 22a is within the XZ plane. The mass analysis magnet 22a is configured to form an ion beam focus point P at the upstream side of the high energy multistage linear acceleration unit 14 as depicted by the dashed line.

The ion beam focus point P is formed between the mass analysis magnet 22a and the beamline component at the downstream side thereof (for example, the entrance Q-lens 174). Thus, "the upstream side of the high energy multistage linear acceleration unit 14" where the focus point P is formed may include the most upstream portion or the entrance of the high energy multistage linear acceleration unit 14. That is, the focus point P is located outside the high energy multistage linear acceleration unit 14 in FIG. 19, but the focus point P may be located inside the high energy multistage linear acceleration unit 14 (for example, the entrance of the high energy multistage linear acceleration unit 14).

FIG. 20 is a view illustrating an ion beam cross-section 306 at the ion beam focus point P. The ion beam cross-section 306 illustrated in FIG. 20 is the cross-section of the ion beam at a plane passing through the focus point P and perpendicular to the ion beam transportation direction (that is, the XY plane).

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The mass analysis magnet 22a focuses the ion beam at the focus point P in the horizontal direction (that is, the X direction). Thus, the focus point P is a horizontal beam focus point.

Thus, the ion beam cross-section 306 has an elongated shape in the vertical direction (the Y direction). The ion beam cross-section 306 has a first beam width W1 and a second beam width W2 in the horizontal direction and the vertical direction, respectively, at the focus point P. The second beam width W2 is longer than the first beam width W1. As shown, the shape of the ion beam cross-section 306 is, for example, an ellipse. The first beam width W1 corresponds to the shortest diameter of the ellipse, and the second beam width W2 corresponds to the longest diameter of the ellipse.

In FIG. 20, the intensity distribution of the ion beam cross-section 306 is depicted by the contour line. Further, the Y-direction intensity distribution 308 corresponding to the contour line is expressed at the right side of the ion beam cross-section 306, and the X-direction intensity distribution 310 is expressed at the lower side of the ion beam cross-section 306. As understood from the drawing, the gradient of the Y-direction intensity distribution 308 at the outer peripheral portion of the ion beam cross-section 306 is smaller than the gradient of the X-direction intensity distribution 310 at the outer peripheral portion of the ion beam cross-section 306.

Further, in FIG. 20, the vertical beam width limitation, which may be referred to as a vertical regulation, according to the embodiment is schematically depicted by solid arrows V, and the horizontal beam width limitation, which may be referred to as a horizontal regulation, is schematically depicted by dashed arrows H. This will be described in detail later.

As illustrated in FIG. 19, the mass analyzer 22 includes the mass analysis slit 22b. In the embodiment, the mass analysis slit 22b is fixed, and hence the slit position and the slit width of the mass analysis slit 22b are fixed. The mass analysis slit 22b is disposed at the focus point P in the Z direction. With respect to the location in the XY plane, the mass analysis slit 22b is disposed so that the aperture center thereof coincides with the center orbit L. The horizontal slit width of the mass analysis slit 22b is set so that a desired mass resolution is obtained. Further, the slit shape of the mass analysis slit 22b may conform with the shape of the ion beam cross-section 306 at the focus point P, for example. Accordingly, the slit shape of the mass analysis slit 22b may have an ellipsoidal shape extending along the vertical direction.

Furthermore, in an embodiment, the mass analyzer 22 may include a plurality of mass analysis slits 22b. The plurality of mass analysis slits 22b may include slits having different positions and/or widths. Further, the plurality of mass analysis slits 22b may have slits having different shapes. One slit which is selected from the plurality of mass analysis slits 22b may be used while being disposed at the center orbit L.

Further, in an embodiment, the mass analysis slit 22b may be of a variable type. In this case, the mass analysis slit 22b may be configured so that the slit position and/or the slit width are adjustable in the ion beam focusing direction at the focus point P, for example. The adjustment of the slit position and/or the slit width may be used for the horizontal regulation of the ion beam.

The beam current adjuster 300 is disposed between two adjacent beamline components (for example, the mass analysis magnet 22a and the entrance Q-lens 174). The variable aperture 302 of the beam current adjuster 300 is disposed immediately downstream of the mass analysis slit 22b. The variable aperture 302 is disposed so as to contact the mass analysis slit 22b at the downstream side of the mass analysis slit 22b or is disposed so as to be adjacent thereto with a slight



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gap therebetween. In this way, the variable aperture **302** is disposed near the focus point P. Furthermore, the variable aperture **302** may be disposed at the focus point P. In that case, the mass analysis slit **22b** may be disposed immediately upstream of the variable aperture **302** and near the focus point P.

Here, a way of disposing of the variable aperture **302** “immediately downstream of the mass analysis slit **22b**” means that no beamline component (that is, the component which applies an electric and/or magnetic action to the ion beam as described above) is provided between the mass analysis slit **22b** and the variable aperture **302**. Thus, the variable aperture **302** may be disposed at any position in the Z direction between the mass analysis slit **22b** and the high energy multistage linear acceleration unit **14** (or the entrance Q-lens **174**). In this way, the variable aperture **302** is disposed at the focus point P or the vicinity thereof.

FIGS. **21A** and **21B** are schematic views illustrating the variable aperture **302** according to the embodiment. FIG. **21A** illustrates a state where the variable aperture **302** is opened, and FIG. **21B** illustrates a state where the variable aperture **302** is closed by a certain degree.

The variable aperture **302** includes a pair of aperture plates **312** which are configured to be movable in the Y direction. As depicted by arrows V in the drawing, the pair of aperture plates **312** are configured to be movable in a symmetric manner with respect to the horizontal plane including the center orbit L, and the variable aperture **302** is provided with a drive unit (not illustrated) for this configuration. That is, when one of the aperture plates **312** moves by a certain distance in the +Y direction towards the center orbit L, the other of the aperture plates **312** moves by the certain distance in the -Y direction towards the center orbit L. In this way, the pair of aperture plates **312** moves by the same distance in the opposite directions.

The variable aperture **302** may be, for example, a CVA (Continuously Variable Aperture). One configuration example of CVA is disclosed in, for example, JP 2000-243341 A and JP 2000-243342 A, the entire contents of which are incorporated herein by reference.

Furthermore, in an embodiment, the variable aperture **302** may include at least one aperture plate which is configured to be movable in a direction perpendicular to the ion beam focusing direction at the focus point P. Thus, the variable aperture **302** may include, for example, a pair of aperture plates having a fixed aperture plate and a movable aperture plate configured to be movable in a direction perpendicular to the focusing direction.

Further, in an embodiment, the variable aperture **302** may include at least one aperture plate which is configured to be rotatable about a rotation axis parallel to the ion beam focusing direction and perpendicular to the transportation direction.

As illustrated in FIGS. **21A** and **21B**, an aperture width **314** is formed between the aperture plates **312** so that an ion beam passes through the aperture width. When the aperture plates **312** move, the aperture width **314** is changed. Since the aperture plates **312** move in the Y direction as described above, the aperture width **314** is variable in the Y direction. When the ion beam passes through the aperture width **314**, the beam width in the Y direction is limited. That is, both ends (the outer portion beyond the aperture width **314**) of the ion beam cross-section **306** (see FIG. **20**) in the Y direction are shielded by the aperture plates **312**, and the center portion of the ion beam cross-section **306** corresponding to the aperture width **314** is directed toward the downstream side of the beamline.

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In this way, the beam current of the ion beam which passes through and exits the variable aperture **302** is reduced compared to that of the ion beam which enters the variable aperture **302**. Thus, when the aperture width **314** is changed, the beam current may be adjusted. The ion beam passing through the variable aperture **302** and thereby allowing the ion beam to have the beam width adjusted in a direction perpendicular to the focusing direction is supplied to the high energy multistage linear acceleration unit **14** (see FIG. **19**).

The high energy ion implanter **100** according to the embodiment is configured to determine the implanting beam current by the variable aperture **302**. The high energy ion implanter **100** is designed so that the beam current amount implanted to the substrate is determined in response to the aperture width **314**. Thus, the ion beam may be controlled so that a desired implanting beam current is applied to the substrate by an appropriate setting of the aperture width **314**.

The variable aperture **302** is configured to determine the implanting beam current based on the beam current measured by the beam current detector, for example, the lateral elongated faraday cup **126**. For that reason, the control device **304** (see FIG. **19**) is configured to set the aperture width **314** based on a measured current of the beam current detector. For example, the control device **304** is configured to change the aperture width **314** so that the measured current matches a target implanting beam current. Here, the implanting beam current means the beam current amount which is implanted into a substrate (for example, the wafer **200** illustrated in FIG. **1**), that is, the beam current amount at the substrate level (in other words, the substrate surface).

Furthermore, the control device **304** may be a control unit for controlling the high energy ion implanter **100** or a part of the control unit. Further, the control device **304** may be a controller dedicated for the beam current adjuster **300** which is provided separately from the control unit.

In a typical arrangement, the ion beam is transported as a beam having a cross-section vertically elongate along the direction perpendicular to a plane including the bending orbit of the mass analysis magnet. A horizontal width limitation aperture is disposed at the exit of the mass analysis magnet to determine the mass resolution of the mass analysis magnet. The horizontal width limitation aperture provides not only the function of determining the mass resolution but also a function of adjusting the beam current. Accordingly, the resultant beam current is adjusted by the horizontal regulation.

Thus, in such a typical arrangement, the adjustment of the aperture needs to be performed in consideration of both the mass resolution and the resultant beam current, and it is not easy to optimally set the aperture along with these factors. For example, when the aperture is narrowed in order to realize a fine mass resolution, the beam current is decreased. Thus, it is difficult to simultaneously obtain both the fine mass resolution and the large beam current.

Further, as described above by referring to FIG. **20**, since the horizontal intensity distribution of the vertically elongate beam has a large gradient, the beam current is sensitive with respect to the horizontal aperture width. Since a large change in beam current occurs due to a slight change in horizontal width, the beam current may not be easily controlled at a target beam current.

Furthermore, when the center of the horizontal aperture width is deviated from the beam center, the beam is asymmetrically shielded at the right and left sides. Hence the beam having passed through the aperture has a new beam center at a position different from the beam not yet having passed therethrough. Since the gradient of the horizontal intensity distribution of the beam is large, the positional deviation

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amount of the beam center may be easily increased between before and after the beam passes through the aperture. In order to decrease the positional deviation amount, there may be a need to perform a beam adjustment operation so that the center of the horizontal aperture width is aligned to the beam center of the beam not yet having passed through the aperture. Since such an operation consumes the time which may be used for the ion implanting process on the wafer **200**, the productivity of the apparatus is affected.

However, in the embodiment, the variable aperture **302** is configured to adjust the beam width in a direction perpendicular to the ion beam focusing direction at the focus point P in order to control the implanting beam current. The implanting beam current is adjusted by the vertical regulation of the variable aperture **302**. As described above by referring to FIG. **20**, since the gradient of the vertical intensity distribution at the outer peripheral portion of the ion beam cross-section **306** is smaller than the gradient of the horizontal intensity distribution at the outer peripheral portion of the ion beam cross-section **306**, the implanting beam current moderately changes with a change in the aperture width **314**. Further, the variable aperture **302** is provided separately from the mass analysis slit **22b**.

Thus, according to the embodiment, the implanting beam current may be easily adjusted to the target implanting beam current by the change of the aperture width **314**. Since the vertical regulation is employed, the controllability of the implanting beam current is improved.

Further, according to the embodiment, since the implanting beam current may be adjusted independently from the mass resolution, both factors may be optimally set.

Furthermore, according to the embodiment, since the positional deviation amount between the beam center of the beam having passed through the aperture and the beam center of the beam not yet having passed through the aperture comparatively decreases, it is advantageous in that the above-described beam adjustment operation may not be needed. The positional deviation amount of the beam centers involves with the positional error and/or the angular error of the beam at the substrate level. An initial amount of the positional deviation may cause a large error at the substrate level as the beam transportation distance increases. Thus, a small amount of the positional deviation is advantageous in an implanter with a long beamline as in the high energy ion implanter **100**.

A further advantage is obtained when the beam width is limited, as in the embodiment, in a direction perpendicular to the focusing direction, that is, a direction in which the gradient of the intensity distribution of the ion beam cross-section **306** is small. The advantage may be that the beam current amount of the ion beam exiting from the beam current adjuster **300** may be insensitive to fluctuations in the ion beam entering into the beam current adjuster **300**. It should be appreciated that the effect on the vertical intensity distribution of the ion beam cross-section **306** is always reduced compared to the effect on the horizontal intensity distribution when the fluctuations occur in e.g., the ion source **10**.

Thus, according to the embodiment, since the beam current at the substrate level may be adjusted in a short time without degrading other beam quality such as mass resolution, it is possible to provide an ion implanter which contributes to the improvement in productivity. Particularly, in the high energy ion implanter **100** of single wafer type, the productivity may be improved.

In an embodiment, the beam current adjuster **300** may be adapted for consecutive or sequential implanting processes (so-called chained implant) in which only the beam current amount is changed on a process-by-process basis. Accord-

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ingly, in a case where only the implanting beam current is changed from a first implanting recipe for a first ion implanting process to a second implanting recipe for a subsequent second ion implanting process, the control device **304** may be configured to adjust the beam width by using the variable aperture **302** in a direction perpendicular to the focusing direction at an interval between the first ion implanting process and the second ion implanting process and to perform the second ion implanting process directly subsequent to the first ion implanting process. In this way, since the subsequent ion implanting process may be started without stopping the implanting process for the beam adjustment operation, this is helpful for the improvement in the productivity.

Furthermore, in this case, the control device **304** may be configured to perform the second ion implanting process subsequently after the first ion implanting process by adjusting at least one implanting condition other than the implanting beam current if necessary between the first ion implanting process and the second ion implanting process.

As described above, the invention has been described based on the embodiments. The invention is not limited to the above-described embodiments, and it is understood by the person skilled in the art that a design may be changed in various forms, various modified examples may be employed, and the modified examples are also included in the scope of the invention.

In the above-described embodiments, the beamline component which forms the ion beam focus point P is disposed at the upstream side of the high energy multistage linear acceleration unit **14**, but the invention is not limited thereto. In an embodiment, the beamline component which forms the ion beam focus point may be disposed at the downstream side of the high energy multistage linear acceleration unit **14**, and the variable aperture may be provided at the focus point or the vicinity thereof.

For example, the variable aperture **302** of the beam current adjuster may be disposed between the high energy multistage linear acceleration unit **14** and a beam focusing/defocusing device **32** which is provided for the high energy ion beam accelerated by the high energy multistage linear acceleration unit **14**. In this case, as illustrated in FIG. **22**, the variable aperture **302** is disposed immediately downstream of the energy analysis slit **28**.

Further, the variable aperture **302** of the beam current adjuster may be disposed between the high energy multistage linear acceleration unit **14** and a beam scanner **34** which is provided for the high energy ion beam accelerated by the high energy multistage linear acceleration unit **14**. In this case, as illustrated in FIG. **23**, the variable aperture **302** may be disposed between a ground electrode **76a** of the beam scanner **34** and a scanning electrode **316**.

In the above-described embodiments, the variable aperture **302** is disposed immediately downstream of the mass analysis slit **22b**, but the invention is not limited thereto. In an embodiment, the variable aperture **302** may be disposed between the mass analysis magnet **22a** and the mass analysis slit **22b**. In this case, the variable aperture **302** may be disposed immediately upstream of the mass analysis slit **22b**, for example.

In the above-described embodiments, the beam current adjuster **300** is provided in the high energy ion implanter **100**, but the invention is not limited thereto. In an embodiment, the beam current adjuster **300** may be provided in an ion implanter which does not have the high energy multistage linear acceleration unit **14**.

It should be understood that the invention is not limited to the above-described embodiment, but may be modified into

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various forms on the basis of the spirit of the invention. Additionally, the modifications are included in the scope of the invention.

What is claimed is:

1. A high energy ion implanter comprising:  
a high energy multistage linear acceleration unit;  
a beamline component arranged upstream or downstream of the high energy multistage linear acceleration unit to form a focus point of an ion beam; and  
a variable aperture device disposed at the focus point or a vicinity thereof to adjust a beam width of the ion beam in a direction perpendicular to a focusing direction of the ion beam at the focus point in order to control an implanting beam current.
2. The high energy ion implanter according to claim 1, wherein the beamline component is arranged so that the focus point is formed upstream of the high energy multistage linear acceleration unit,  
wherein the variable aperture device is disposed downstream of the beamline component so that the ion beam having the beam width adjusted in the direction perpendicular to the focusing direction as a result of passing through the variable aperture device is supplied to the high energy multistage linear acceleration unit.
3. The high energy ion implanter according to claim 1, wherein the beamline component is a mass analyzer comprising a mass analysis slit, and the variable aperture device is disposed immediately downstream of the mass analysis slit.
4. The high energy ion implanter according to claim 1, further comprising a control device that adjusts the beam width in the direction perpendicular to the focusing direction by using the variable aperture device at an interval between a first ion implanting process and a subsequent second ion implanting process and performs the second ion implanting process directly subsequent to the first ion implanting process in a case where the implanting beam current is changed from a first implanting recipe for the first ion implanting process to a second implanting recipe for the second ion implanting process.
5. The high energy ion implanter according to claim 1, further comprising a beam focusing/defocusing device provided for a high energy ion beam accelerated by the high energy multistage linear acceleration unit,  
wherein the variable aperture device is disposed between the high energy multistage linear acceleration unit and the beam focusing/defocusing device.

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6. The high energy ion implanter according to claim 1, further comprising a beam scanner provided for a high energy ion beam accelerated by the high energy multistage linear acceleration unit,  
wherein the variable aperture device is disposed between the high energy multistage linear acceleration unit and the beam scanner.
7. The high energy ion implanter according to claim 1, wherein the high energy ion implanter is designed so that the implanting beam current is determined in response to an aperture width of the variable aperture device.
8. The high energy ion implanter according to claim 7, further comprising a beam current detector that may be arranged downstream of the variable aperture device to measure the implanting beam current,  
wherein the variable aperture device determines the implanting beam current based on a measured beam current of the beam current detector.
9. The high energy ion implanter according to claim 1, wherein the variable aperture device is disposed immediately upstream of a mass analysis slit.
10. The high energy ion implanter according to claim 3, wherein the mass analysis slit includes a fixed slit.
11. The high energy ion implanter according to claim 3, wherein a slit position and/or a slit width of the mass analysis slit is adjustable in the focusing direction.
12. The high energy ion implanter according to claim 1, wherein the variable aperture device comprises at least one aperture plate arranged movable in the direction perpendicular to the focusing direction.
13. The high energy ion implanter according to claim 1, further comprising a high energy beam deflection unit that redirects a high energy ion beam accelerated by the high energy multistage linear acceleration unit toward a substrate.
14. A beam current adjustment method for a high energy ion implanter with a high energy multistage linear acceleration unit, comprising:  
focusing an ion beam at a focus point formed upstream or downstream of the high energy multistage linear acceleration unit; and  
adjusting a beam width of the ion beam in a direction perpendicular to a focusing direction of the ion beam by using a variable aperture device disposed at the focus point or a vicinity thereof in order to control an implanting beam current.

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